



**National Science Center**  
Kharkov Institute of Physics and Technology

# **Bent crystal as an efficient tool for high-energy particle beam control**

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*TES HEP, Poltava, 2018*

# Charged-particle motion in the field of crystal atomic strings



$$N_c Z Z_p e^2 / \hbar c \gg 1$$

$$N_c = R / (a \psi)$$

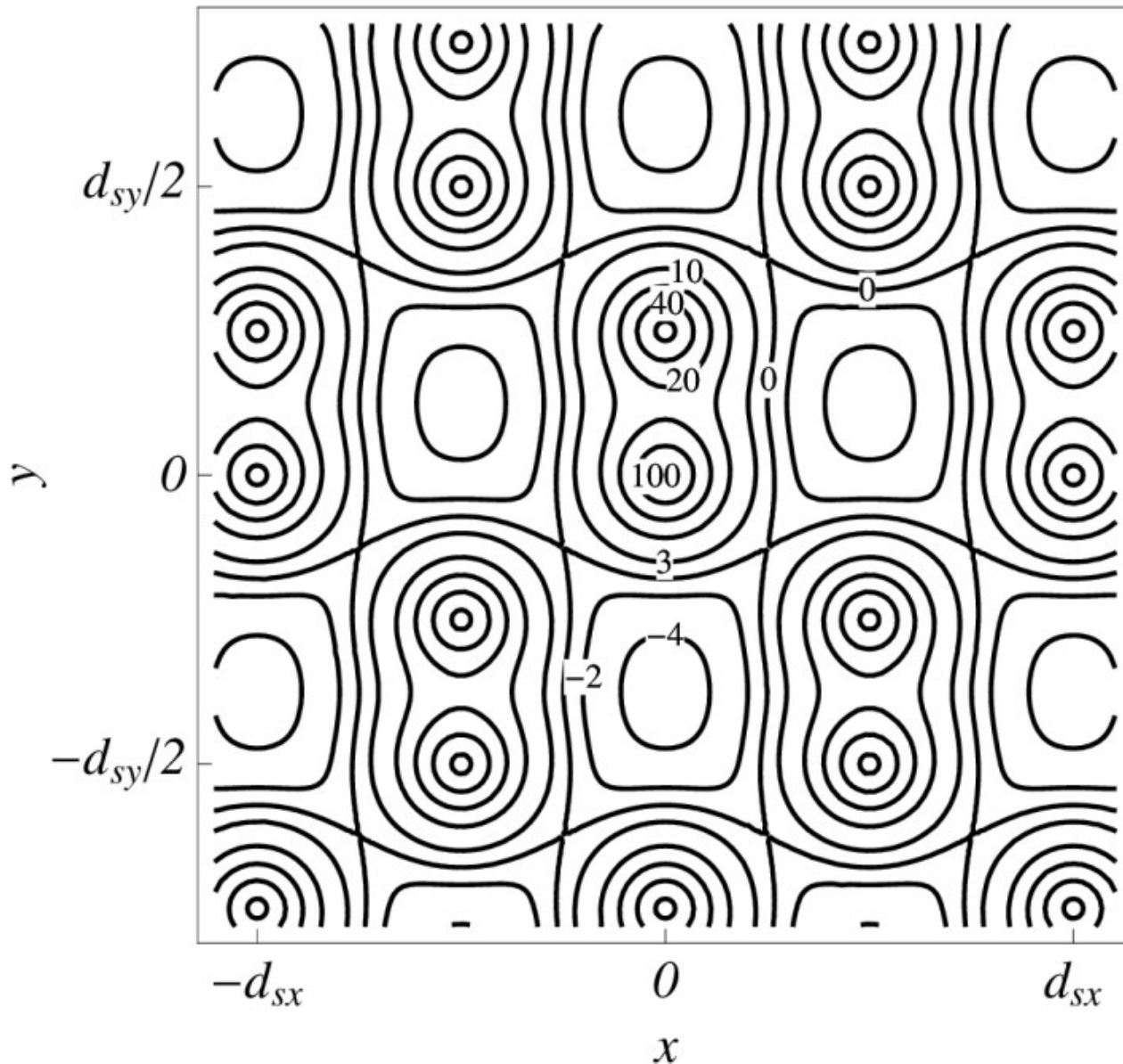
$$\frac{d}{dt} \frac{m v}{\sqrt{1 - v^2 / c^2}} = -q \nabla \Phi_c(\mathbf{r})$$

$$\Phi_c(\mathbf{r}) = \sum_n \Phi_a(\mathbf{r} - \mathbf{r}_n)$$

$$\Phi(\rho) = \frac{1}{L} \int_{-\infty}^{\infty} dz \Phi_c(\rho, z)$$

$$\ddot{\rho} = -\frac{c^2 q}{E_{\parallel}} \frac{\partial}{\partial \rho} \Phi(\rho)$$

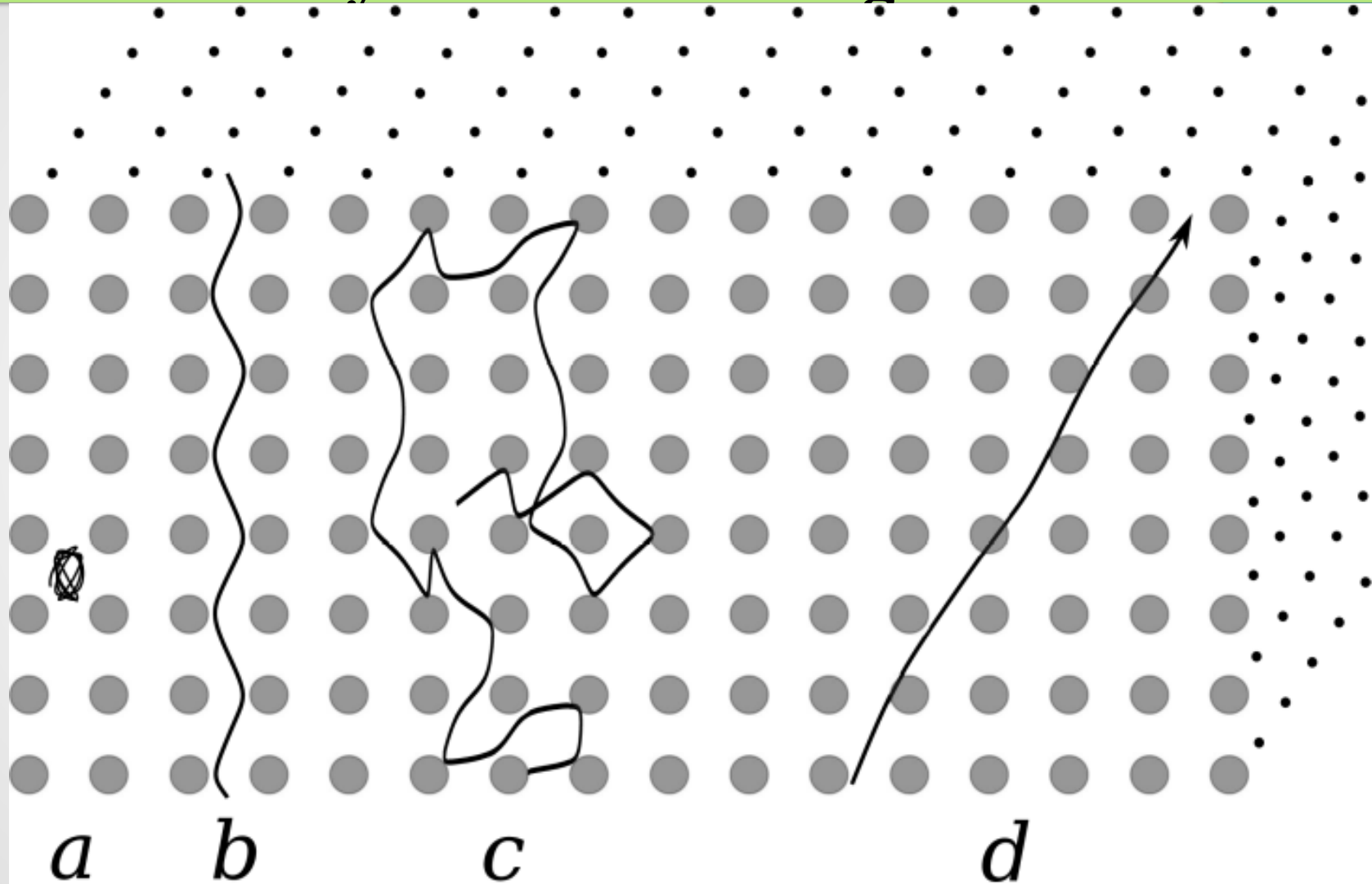
# Charged-particle motion in the field of crystal atomic strings



$$\Phi(\rho) = \frac{1}{L} \int_{-\infty}^{\infty} dz \Phi_c(\rho, z)$$

$$\varepsilon_{\perp} = \frac{E \dot{\rho}^2}{2c^2} + U(x, y)$$

# Regimes of charged-particle motion in the field of crystal atomic strings

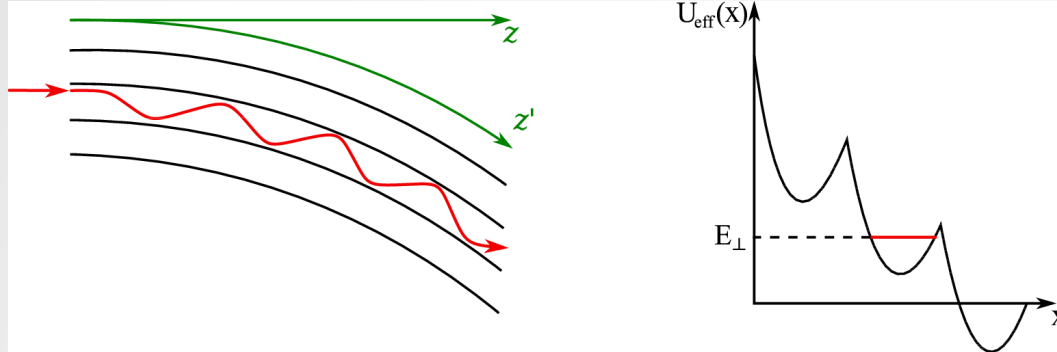


*a)* axial channeling  
*c)* stochastic scattering

*b)* planar channeling  
*d)* strongly above-barrier motion

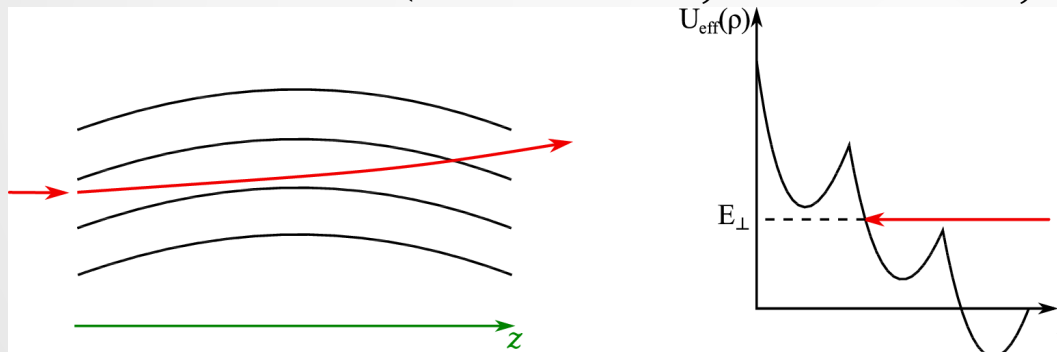
# Mechanisms of deflection of charged particles by a bent crystal

- Planar channeling (*E.N. Tsyganov, 1976*)



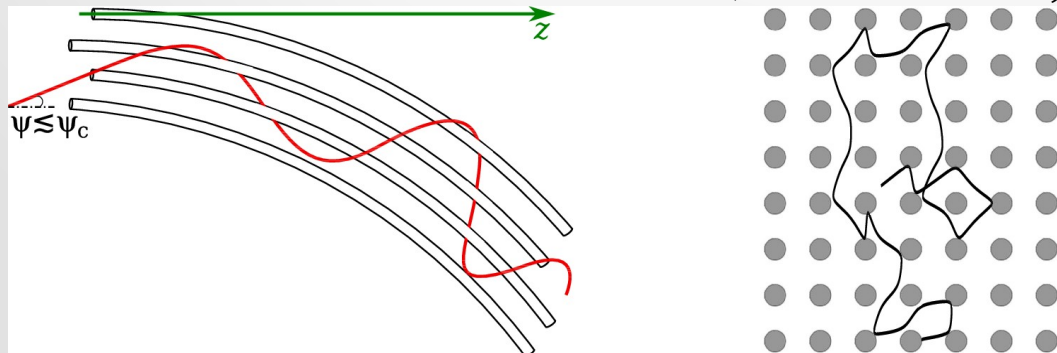
1979 — JINR  
1980 — CERN

- Volume reflection (*A.M. Taratin, S.A. Vorobiev, 1987*)



2006 — IHEP  
2006 — PNPI  
2007 — CERN

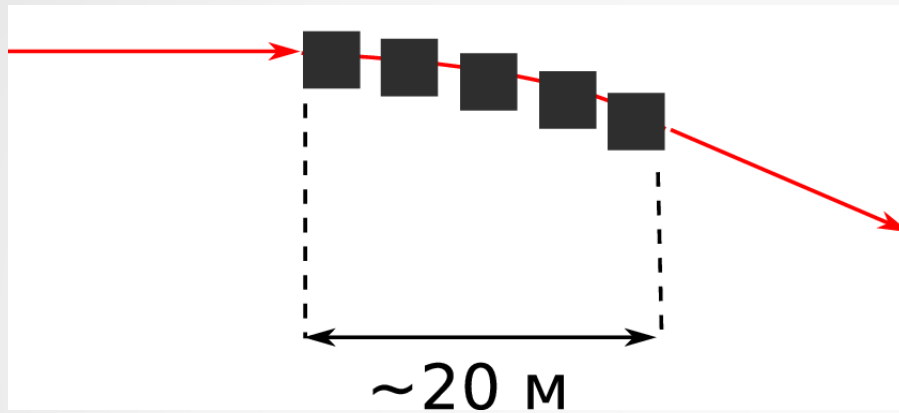
- Stochastic deflection mechanism (*A.A. Grinenko, N.F. Shul'ga, 1991*)



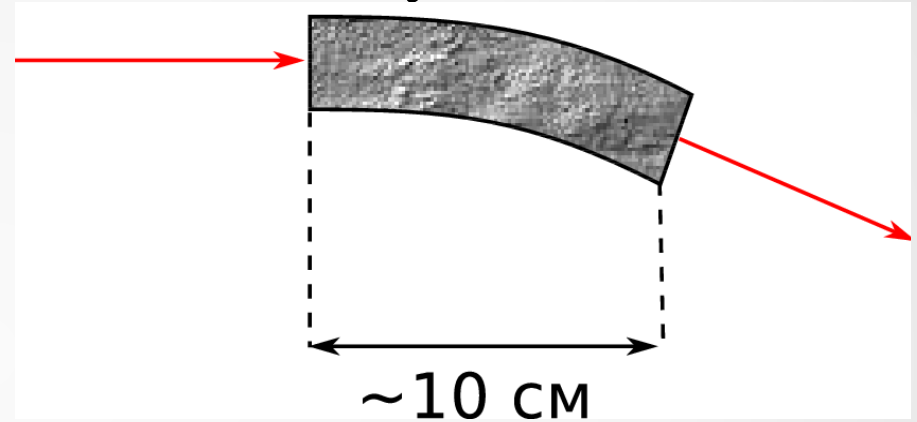
2008 — CERN, protons  
2009 — CERN,  $\pi^-$ -mesons

# Charged particle beam deflection

Magnets

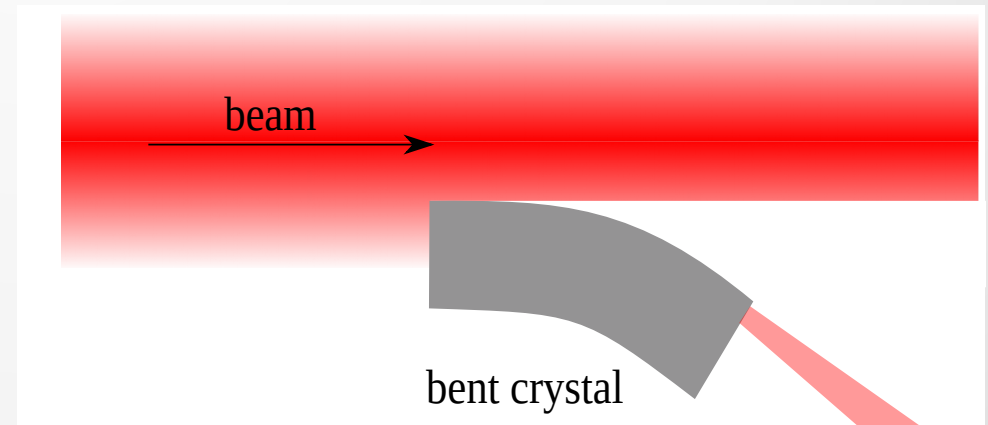


Bent crystal



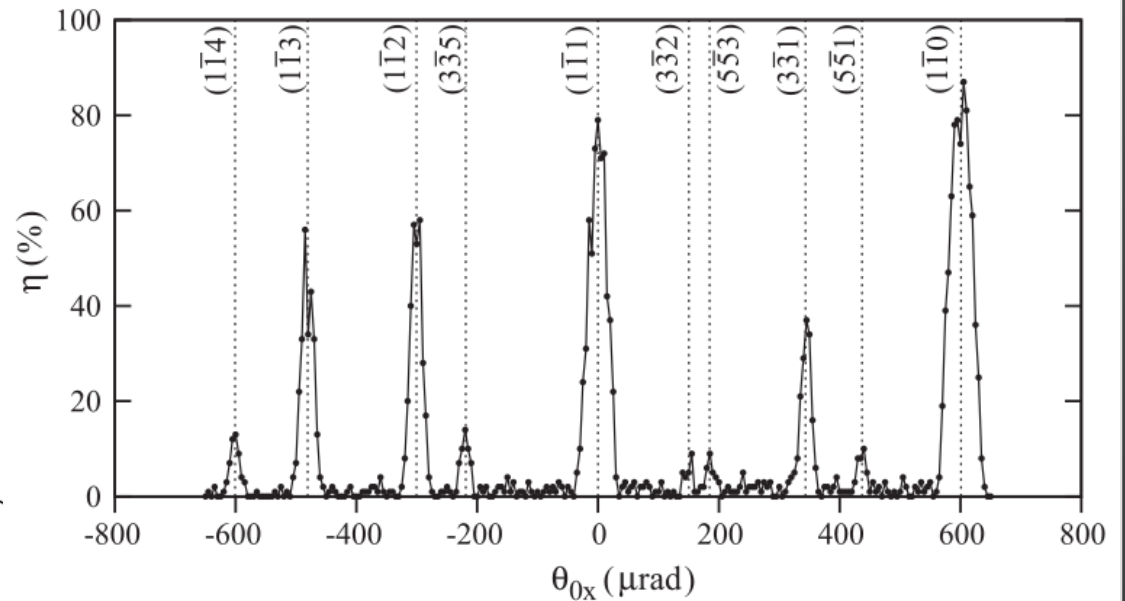
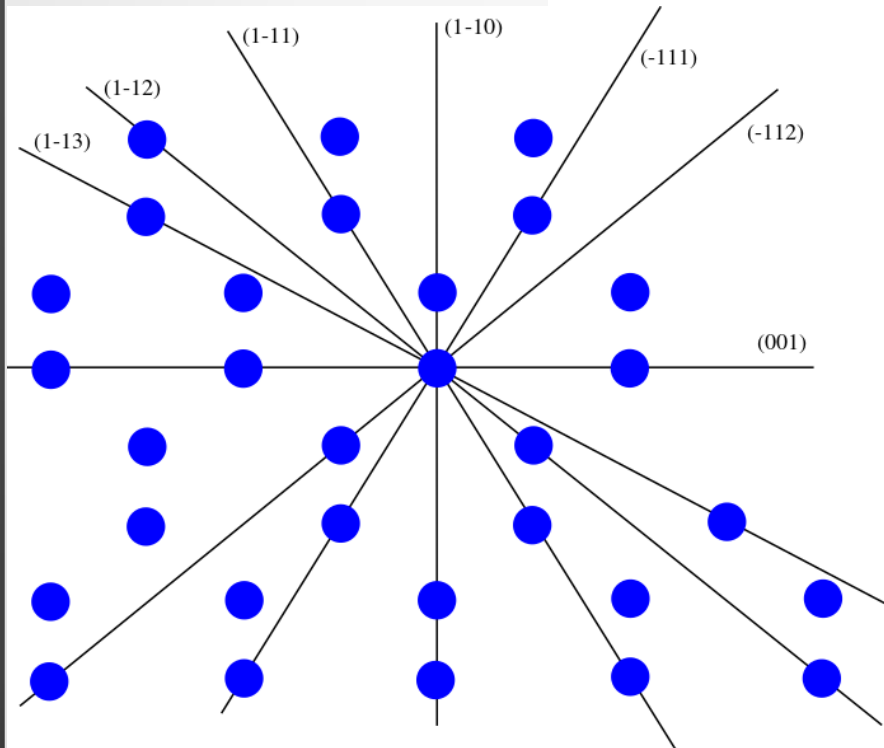
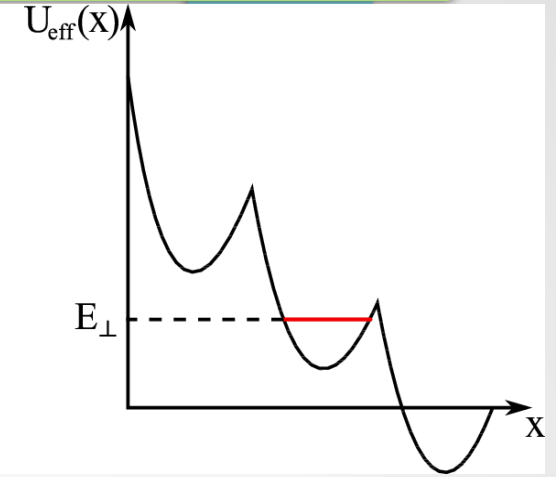
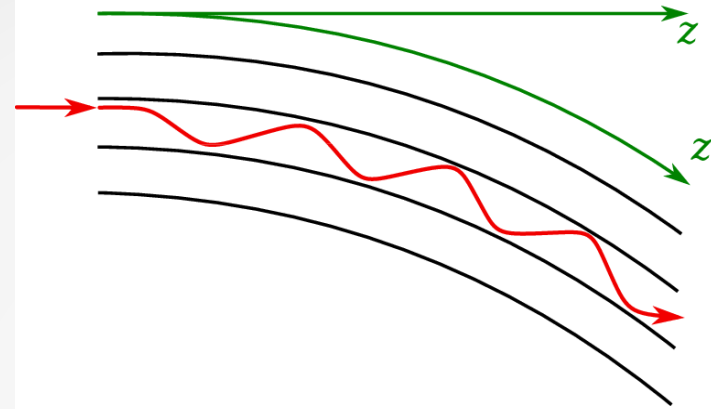
Advantages of bent crystals in front of magnets:

- compact size
- do not need electric power consumption
- do not need cooling



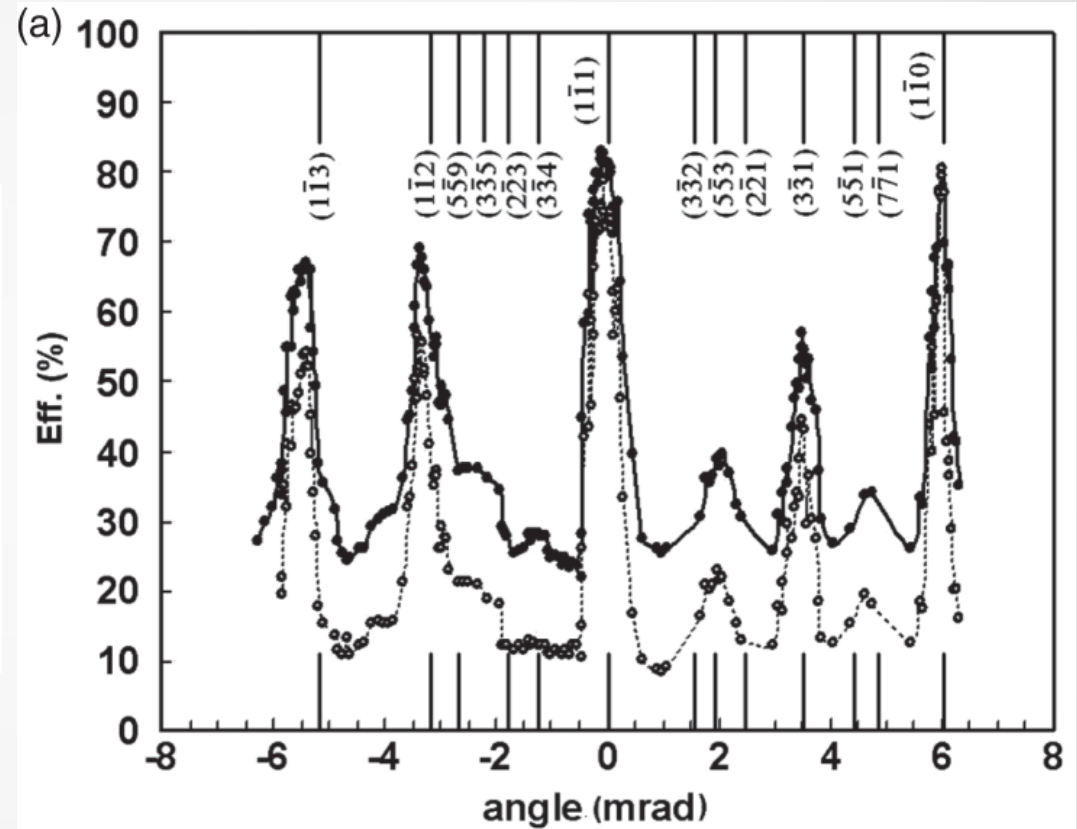
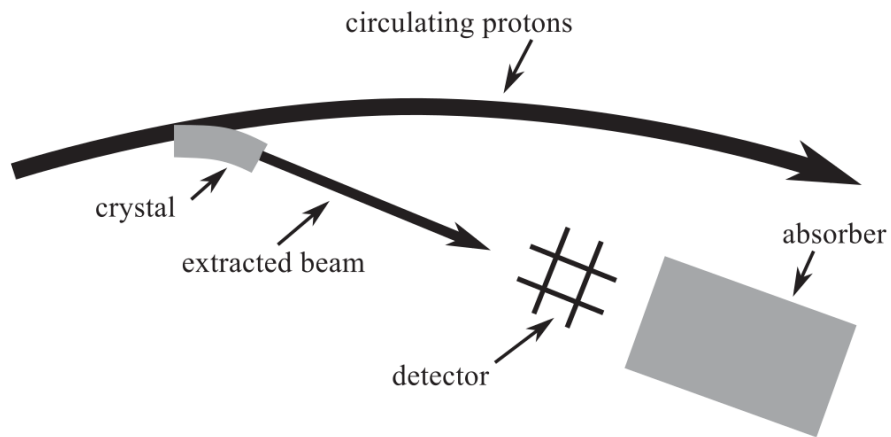
The electric field strength  $\sim 10^{10} \text{ V/cm}$

# Planar channeling in a bent crystal





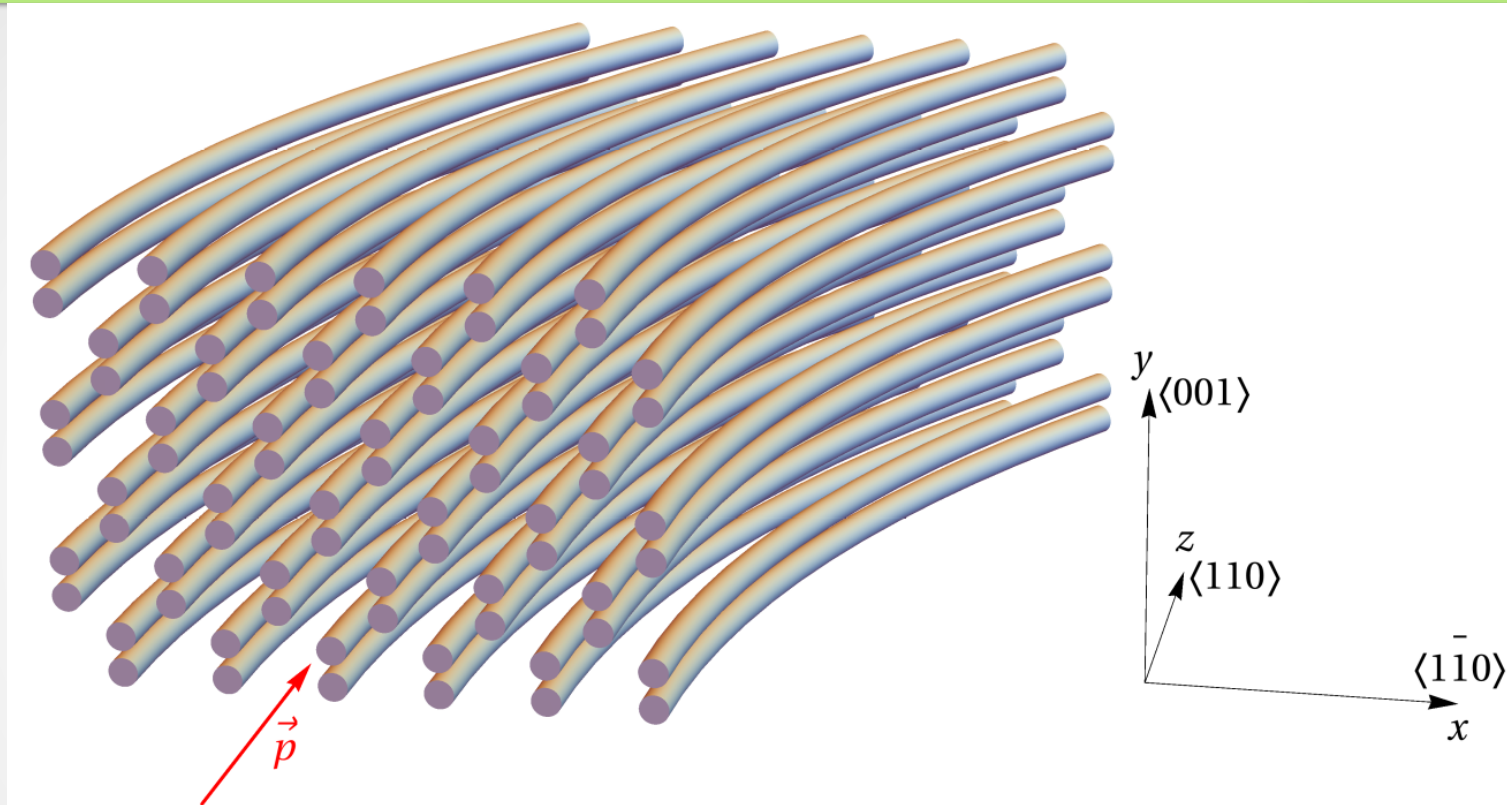
# Planar channeling in a bent crystal



*A.G. Afonin et al. Phys. Rev. ST  
Accel. Beams 15 (2012) 081001*



# Stochastic deflection mechanism



Greenenko-Shul'ga criterion: 
$$\frac{l}{R \psi_c} \frac{L}{R \psi_c} < 1$$

$R$  is crystal curvature radius;

$\psi_c$  is the critical angle of axial channeling;

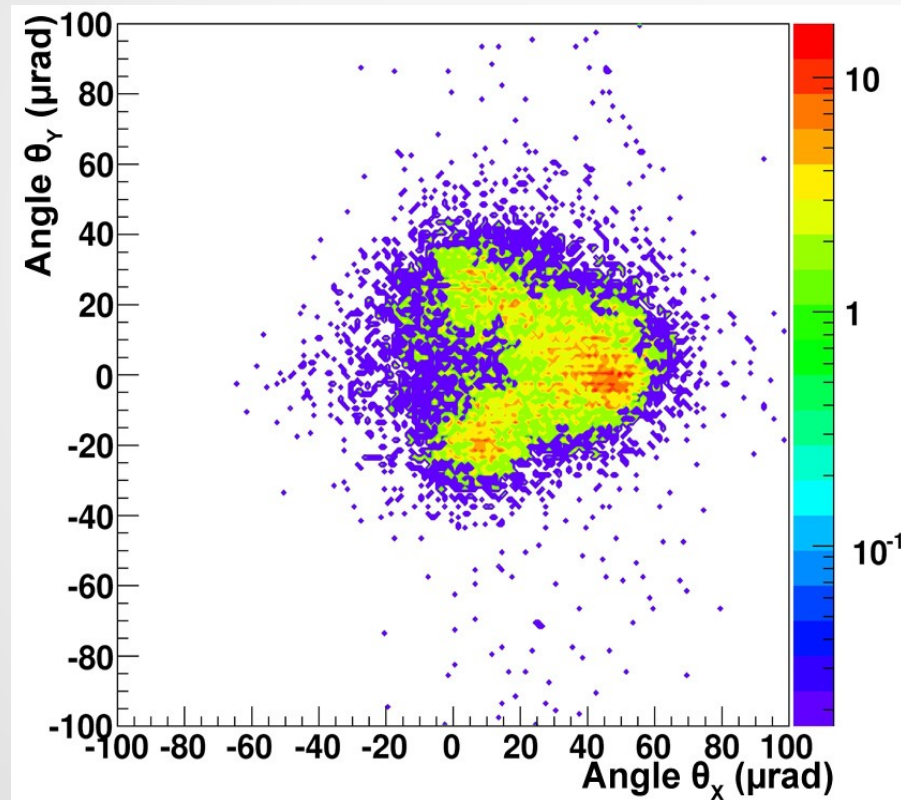
$l$  is the mean free path between successive collisions with atomic strings;

$L$  is the thickness of the crystal.

# Stochastic mechanism of high energy charged particles deflection by bent Si crystal with $R=40$ m

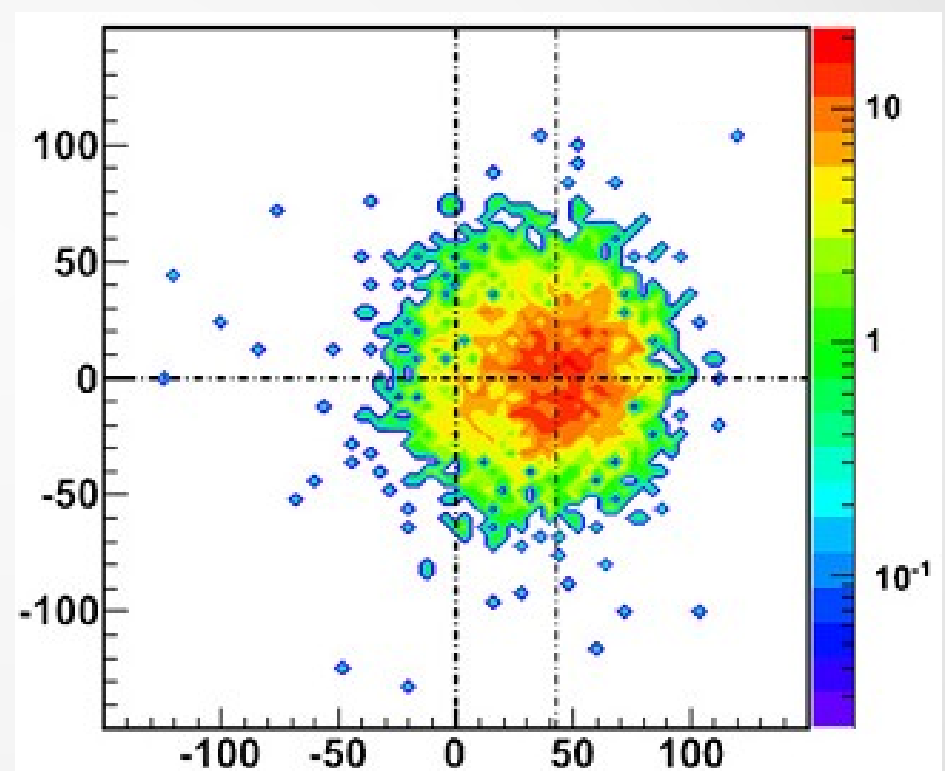
*CERN experiment, UA9 collaboration*

$p^+$ ,  $E=400$  GeV



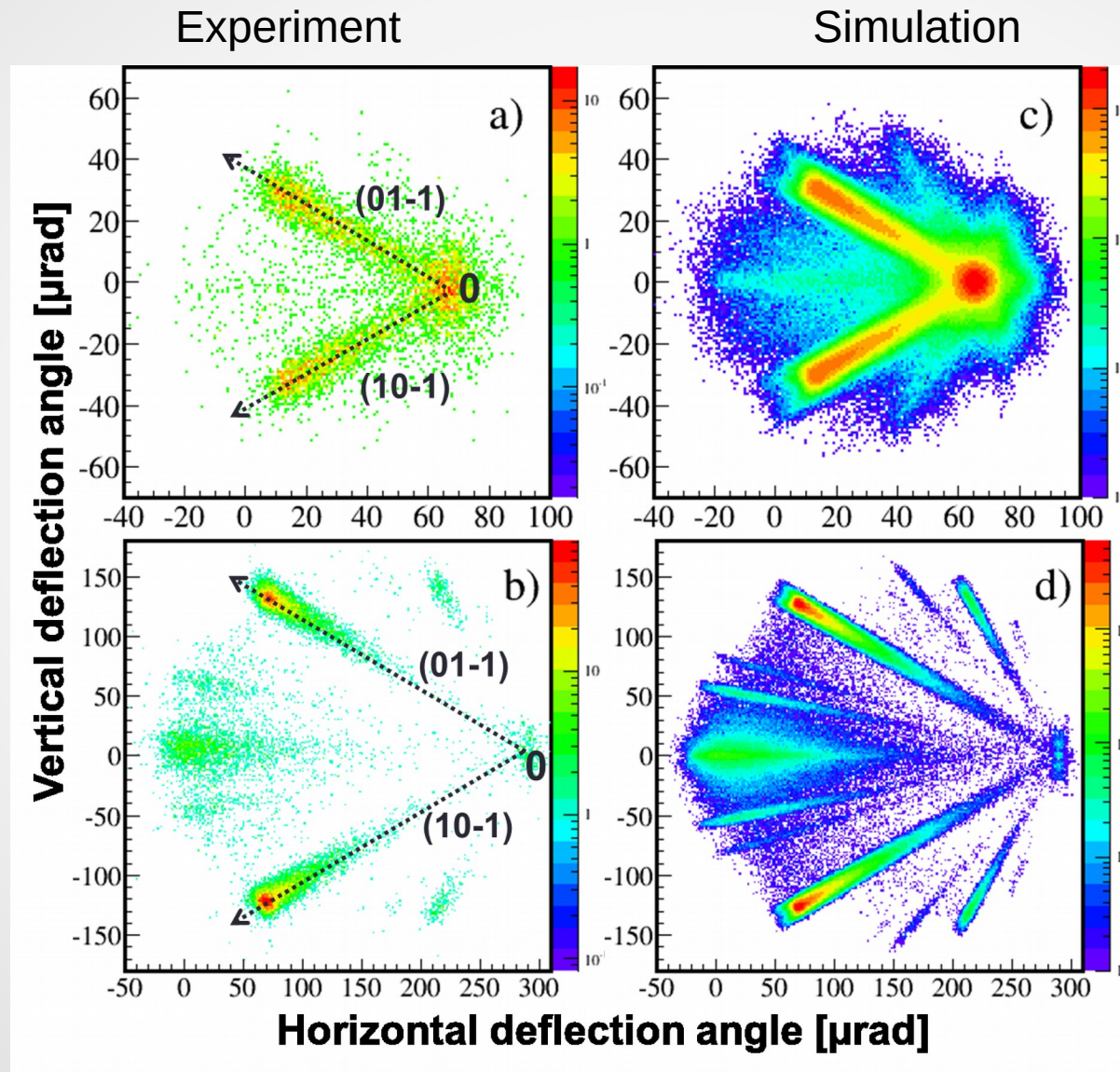
*W. Scandale et al. Phys. Rev. Lett.  
101 (2008), 164801*

$\pi^-$ ,  $E=150$  GeV



*W. Scandale et al. Physics Letters  
B 680 (2009) 301*

# Stochastic deflection and beam splitting



$R = 30,3 \text{ m}$

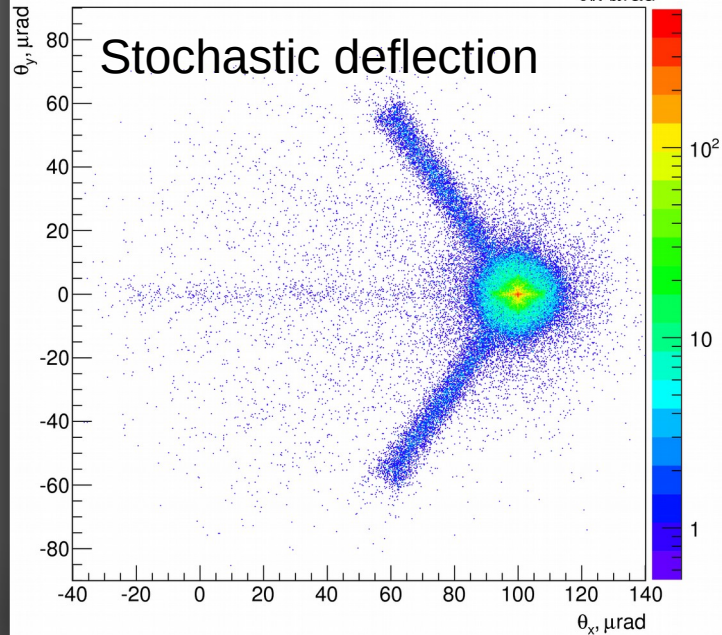
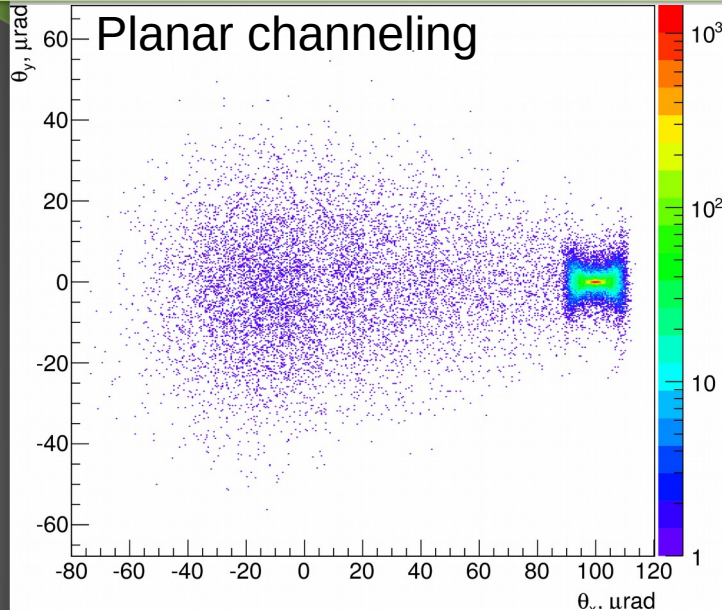
$R = 6,9 \text{ m}$

$p^+$ ,  $E = 400 \text{ GeV}$

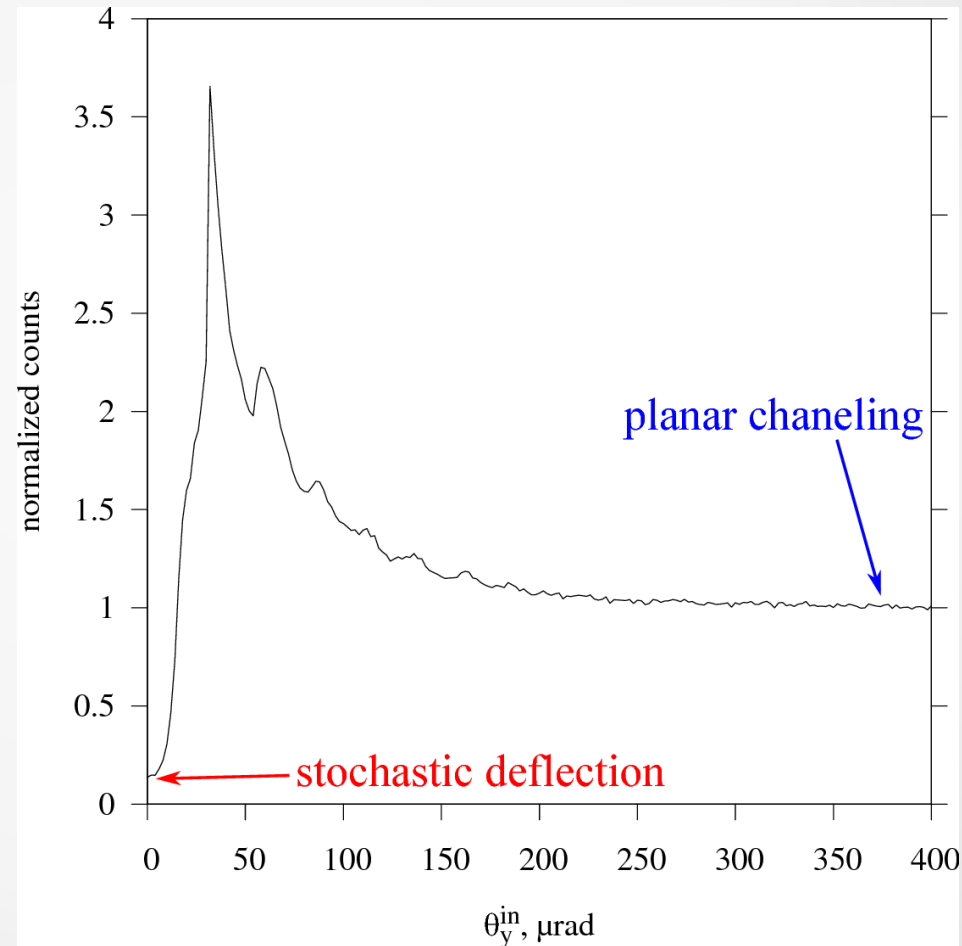


# Close collisions probability

$$\frac{W_{pl}}{W_{ax}} = \frac{a}{\pi r_T} \gg 1$$



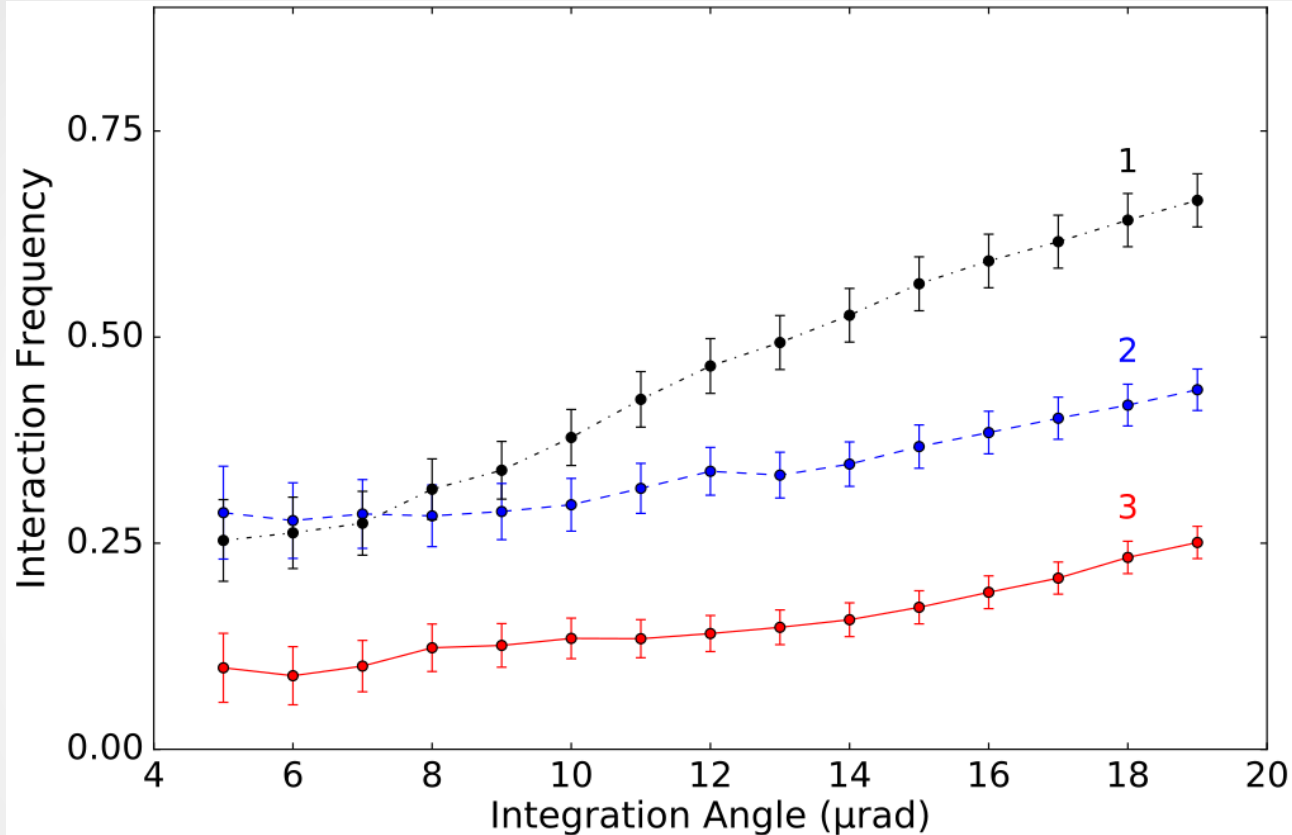
**p<sup>+</sup>, 270 GeV, Si <110>, L = 5 mm, R = 50 m**



*Yu.A. Chesnokov, I.V. Kirillin, W. Scandale, N.F. Shul'ga, V.I. Truten' . Physics Letters B 731 (2014) 118*

# Experimental verification

(W. Scandale et al. / *Physics Letters B* 760 (2016) 826)



**Fig. 5.** Measured inelastic nuclear interaction (INI) frequency of 400 GeV/c protons interacting with the  $\langle 111 \rangle$  and  $\langle 110 \rangle$  crystals as a function of the angular region around the  $\langle 110 \rangle$  planar channeling (black dash-dotted line, 1), the  $\langle 111 \rangle$  axial channeling (blue dashed line, 2) and  $\langle 110 \rangle$  (red continuous line, 3) orientations. The values are normalized to the INI frequencies for the amorphous crystal orientation. (For interpretation of the references to color in this figure legend, the reader is referred to the web version of this article.)

## Influence of incoherent scattering on stochastic deflection of high-energy negative particle beams in bent crystals

$$\frac{d}{dz} \overline{\psi^2} = \frac{l}{R^2} + \frac{d}{dz} \overline{\psi_{inc}^2}$$

$$\text{For } U_{str}(\rho) = U_0 \left( \frac{a}{\rho} \right)^2 \quad l \approx \frac{1}{4nd a} \sqrt{\frac{E}{U_0}} \quad \Rightarrow \quad \overline{\psi^2} = \frac{lL}{R^2} + \overline{\psi_{inc}^2}$$

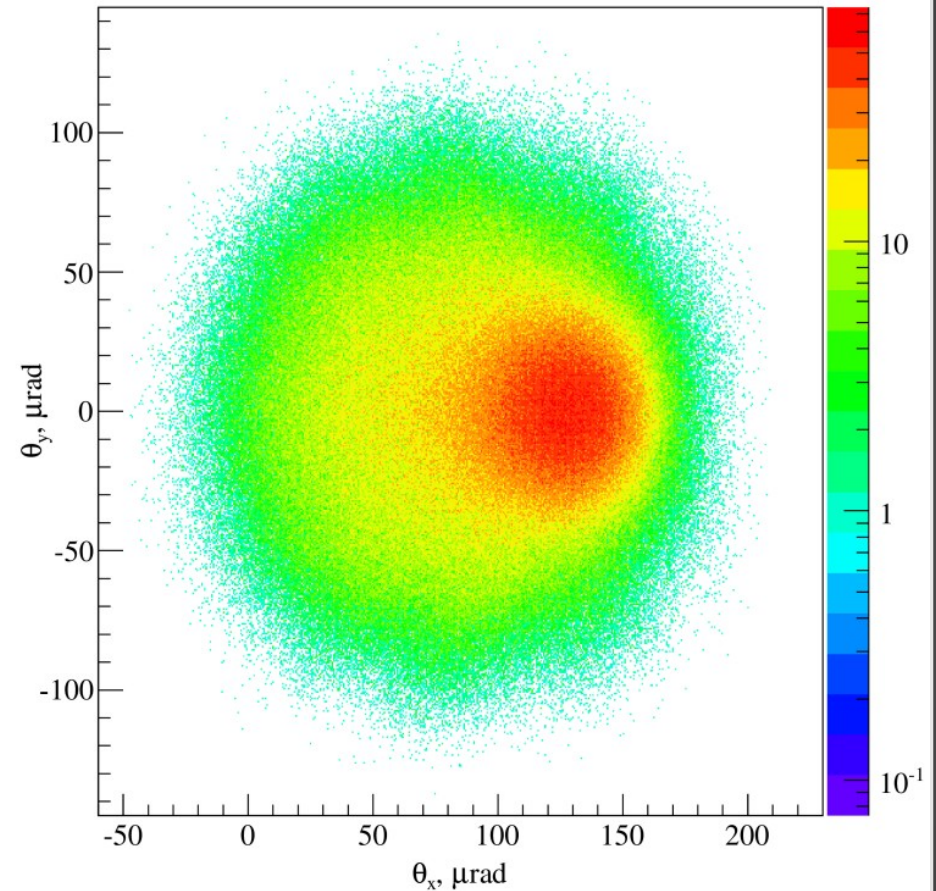
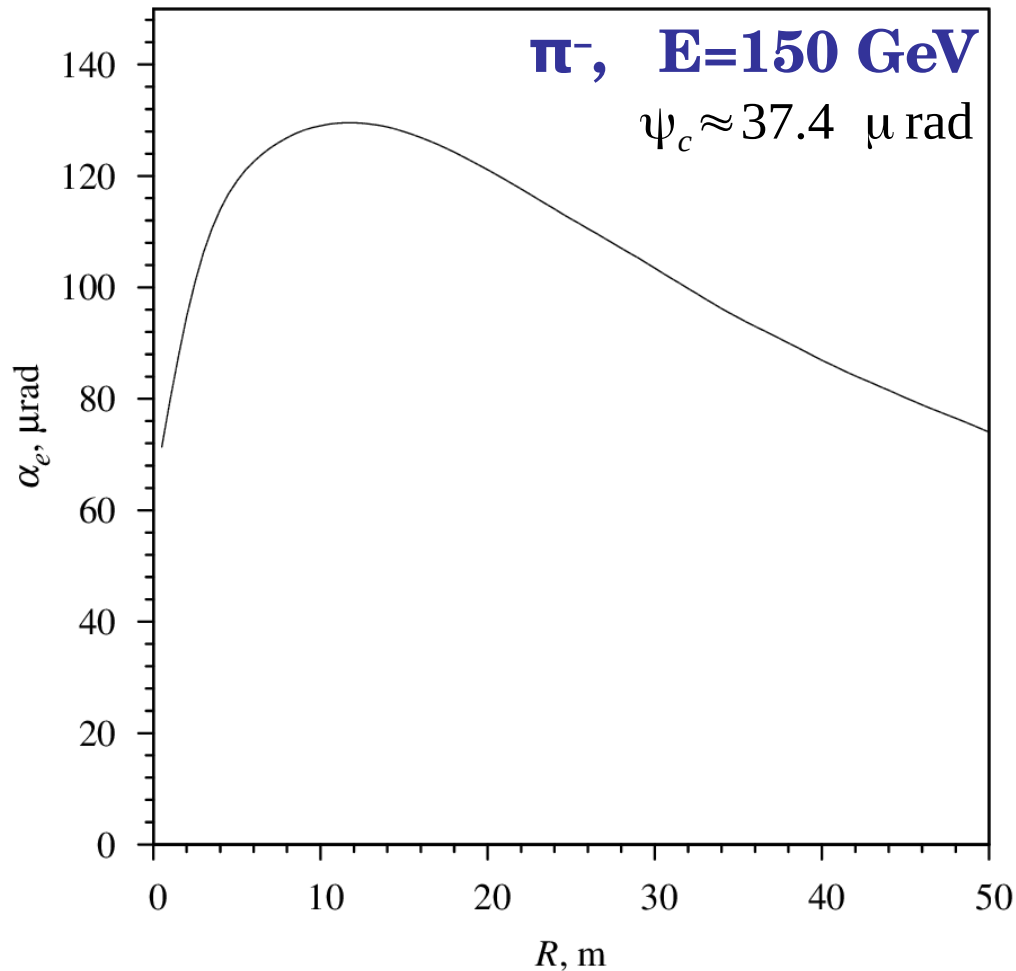
$$\overline{\psi_{inc}^2} = \xi L \quad L_{st} = \frac{\psi_m^2}{l/R^2 + \xi}$$

$$\alpha_{st} = \frac{L_{st}}{R} = \frac{\psi_m^2}{l/R + \xi R}$$

$$\text{For } U_{str}(\rho) = U_0 \left( \frac{a}{\rho} \right)^2 \quad R_{opt} = \sqrt{\frac{l}{\xi}}$$

*I.V. Kirillin, N.F. Shul'ga, L. Bandiera, V. Guidi, A. Mazzolari  
Eur. Phys. J. C 77 (2017) 117*

# Influence of incoherent scattering on stochastic deflection of high-energy negative particle beams in bent crystals



$\pi^-$ ,  $E=150$  GeV, Si  $\langle 110 \rangle$ ,  
 $L=1.52$  mm,  $R=11.7$  m

*I.V. Kirillin, N.F. Shul'ga, L. Bandiera, V. Guidi, A. Mazzolari*  
*Eur. Phys. J. C 77 (2017) 117*



# Dependence of the efficiency of stochastic mechanism of charged particle beam deflection on the particle energy

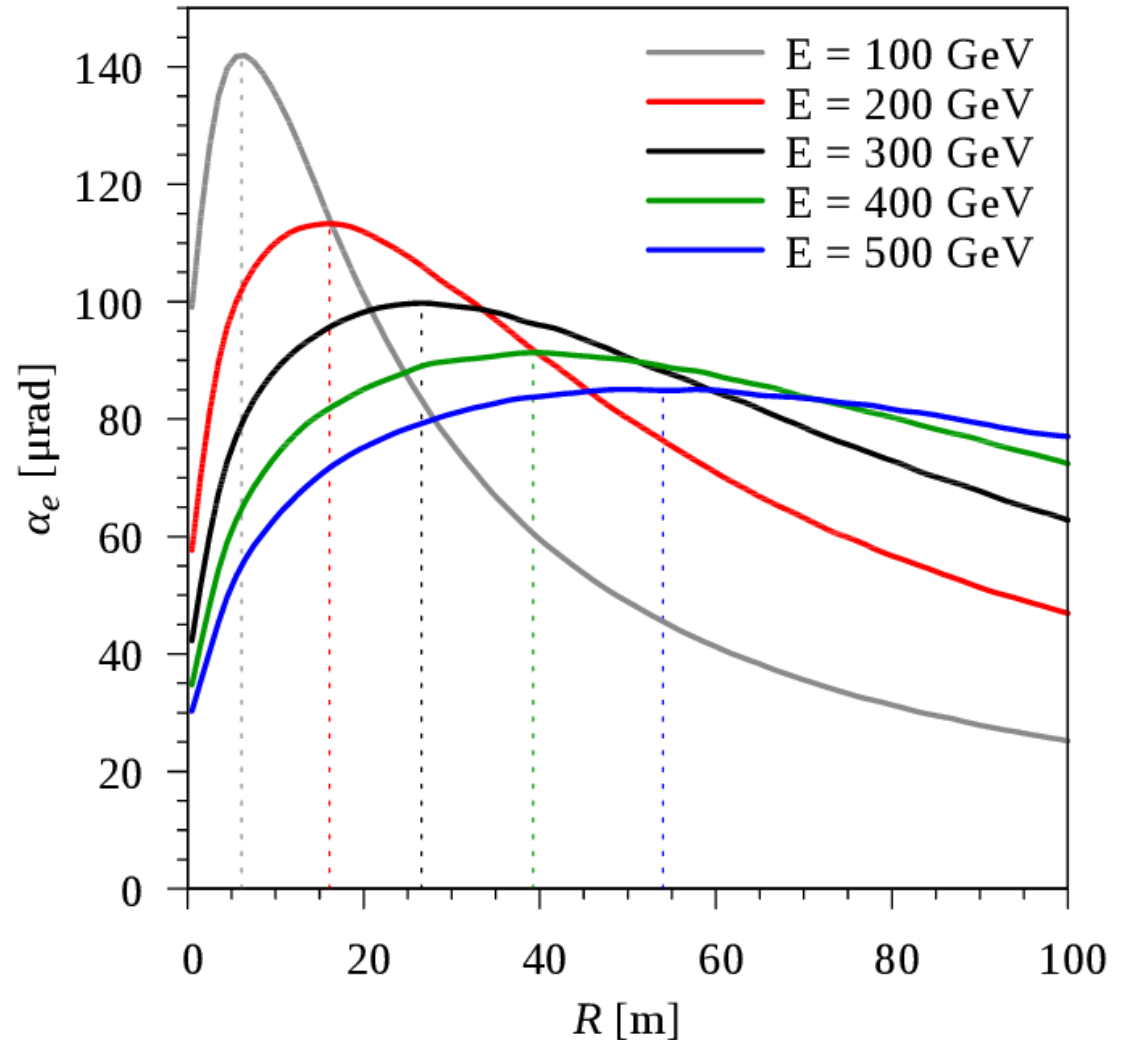
$$\alpha_{st} = \frac{\psi_m^2}{l/R + \xi R}$$

$$\psi_m^2 \propto \frac{1}{E}, \quad \xi \propto \frac{1}{E^2}$$

For  $U_{str}(\rho) = U_0 \left( \frac{a}{\rho} \right)^2 \quad l \propto \sqrt{E}$

$$R_{opt} \propto \sqrt{\frac{l}{\xi}} \propto E^{5/4}$$

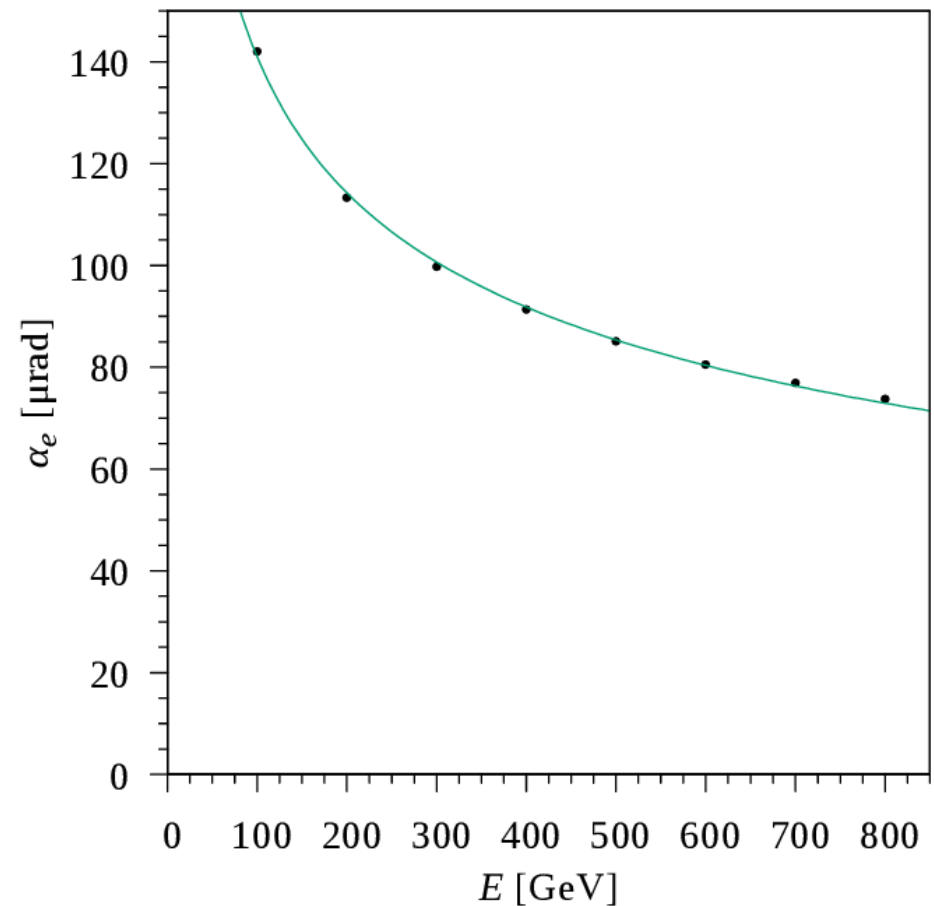
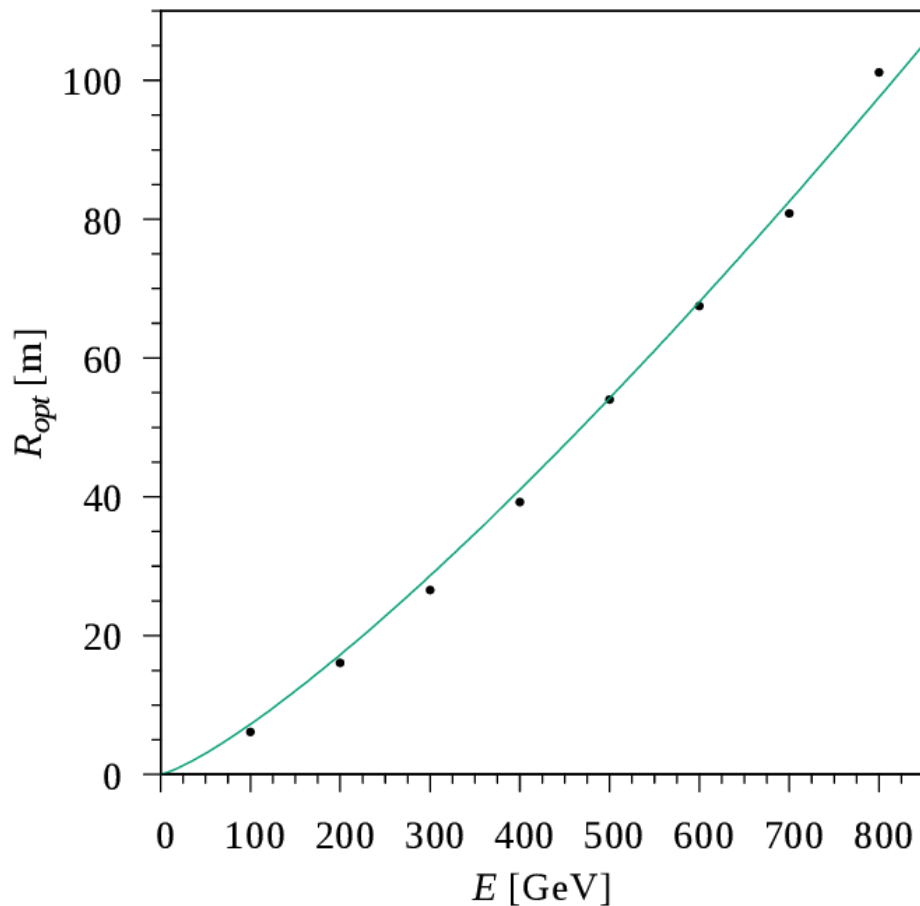
$$\alpha_e \propto \frac{E^{-1}}{E^{-3/4}} \propto E^{-1/4}$$



# Dependence of the efficiency of stochastic mechanism of charged particle beam deflection on the particle energy

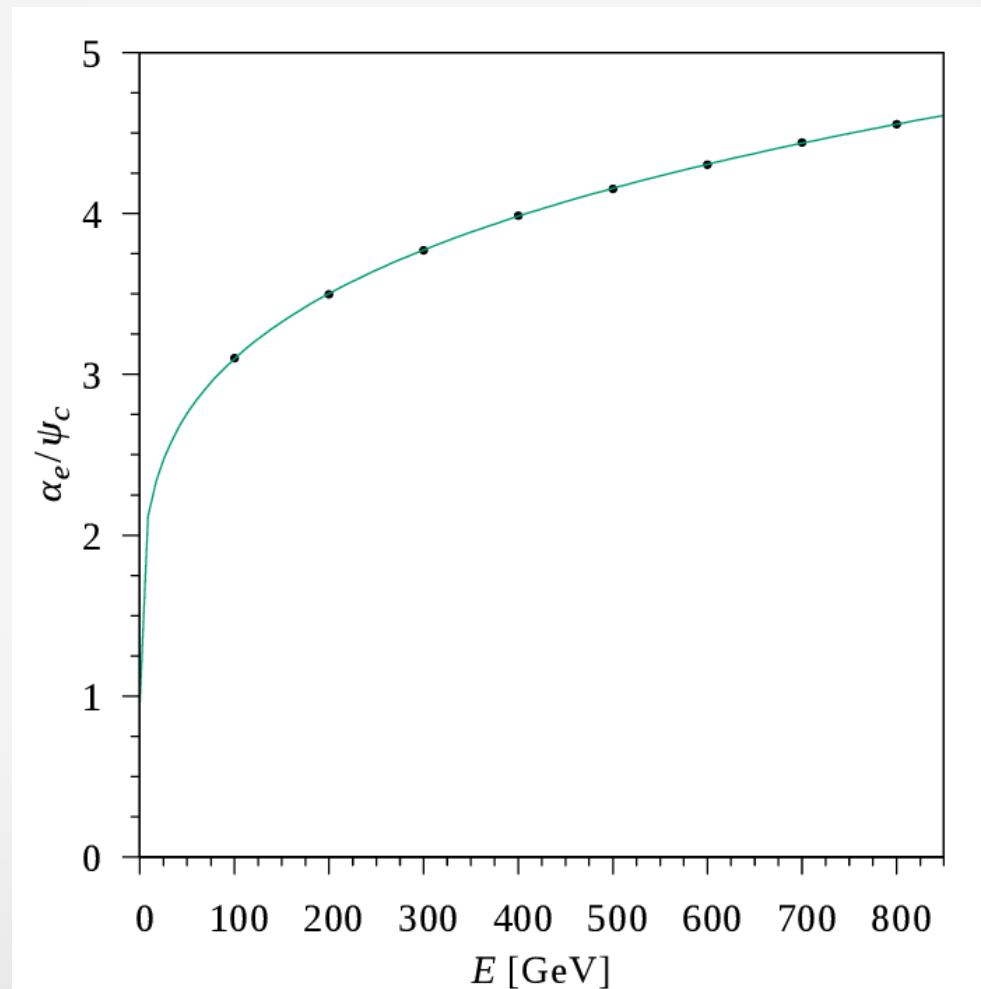
$$R_{opt} \propto \sqrt{\frac{l}{\omega}} \propto E^{5/4}$$

$$\alpha_e \propto E^{-1/4}$$



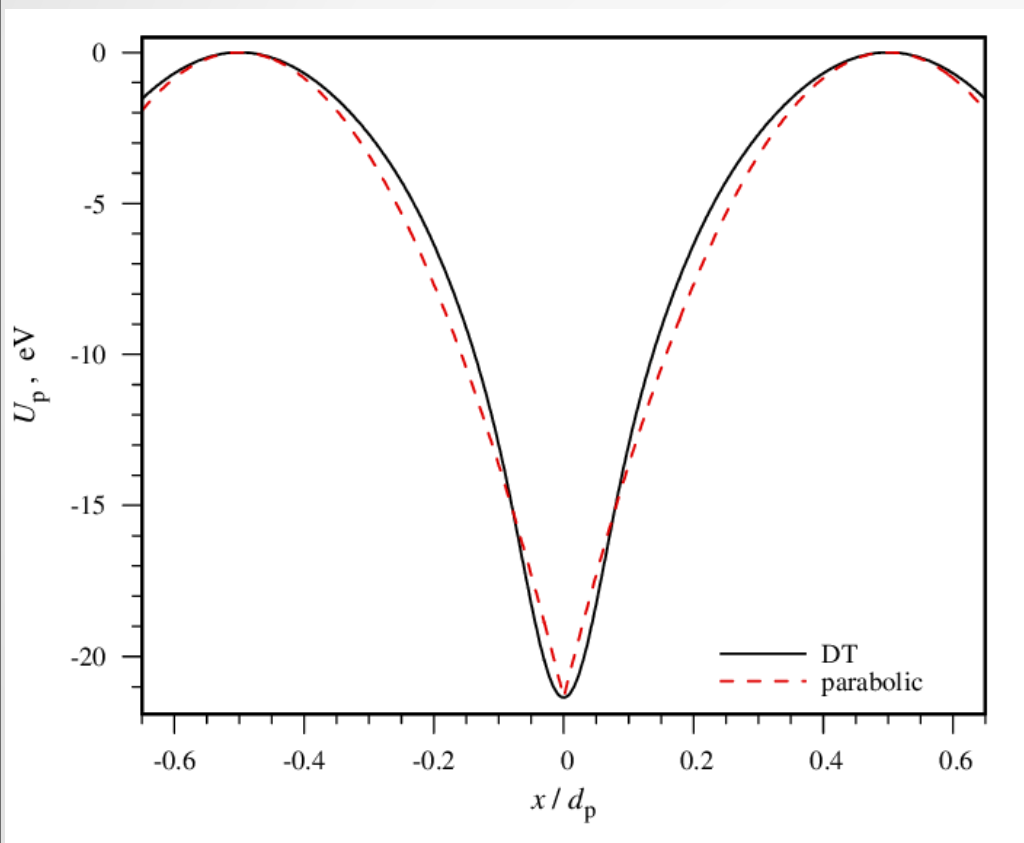
# Dependence of the efficiency of stochastic mechanism of charged particle beam deflection on the particle energy

$$\alpha_e/\psi_c \propto E^{1/4}$$



# Influence of incoherent scattering on planar channeling of high-energy negative particle beams in bent crystals

$$\frac{d^2 x}{dt^2} = -\frac{c^2}{E} \frac{d}{dx} \left( U_p(x) + E \frac{x}{R} \right)$$



$$f = \left( 1 - \sqrt{\frac{R}{R_c}} \right) \frac{1}{\sqrt{2\pi}\theta_0} \int_{-\theta_c}^{\theta_c} \exp\left(-\frac{\theta^2}{2\theta_0^2}\right) d\theta =$$

$$= \left( 1 - \sqrt{\frac{R}{R_c}} \right) \operatorname{erf}\left(-\frac{\theta_c}{\sqrt{2}\theta_0}\right)$$

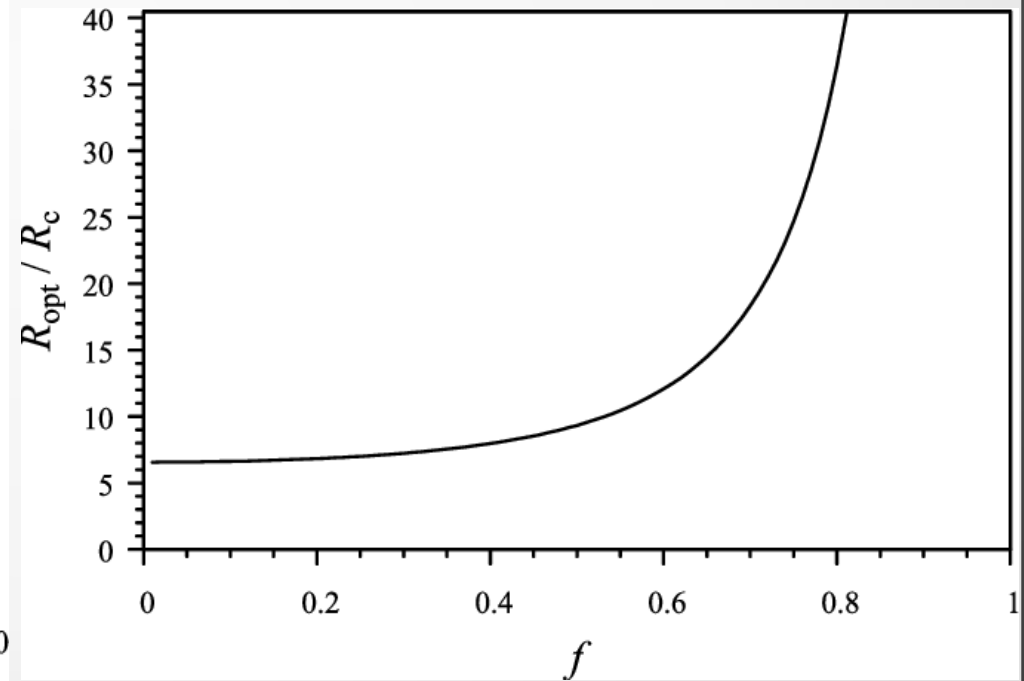
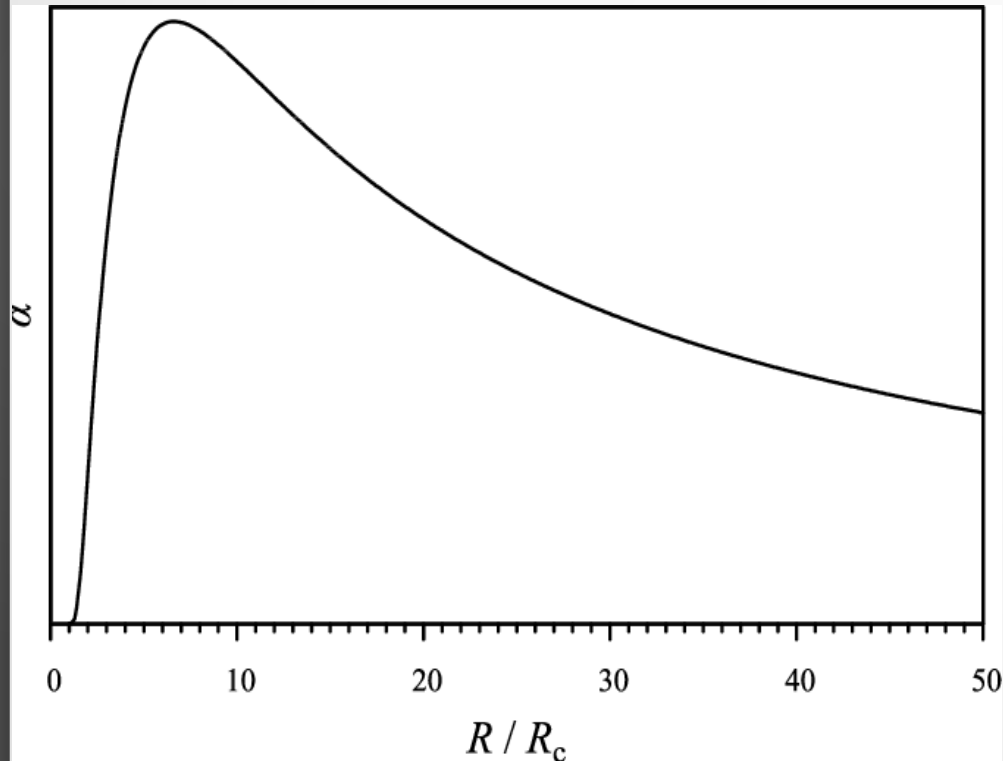
if  $\theta_0 = \xi \sqrt{L}$ , then

$$L = \frac{\theta_c^2}{2\xi^2 \left( \operatorname{erf}^{-1}\left( \frac{f}{1 - \sqrt{\frac{R_c}{R}}} \right) \right)^2}$$

# Influence of incoherent scattering on planar channeling of high-energy negative particle beams in bent crystals

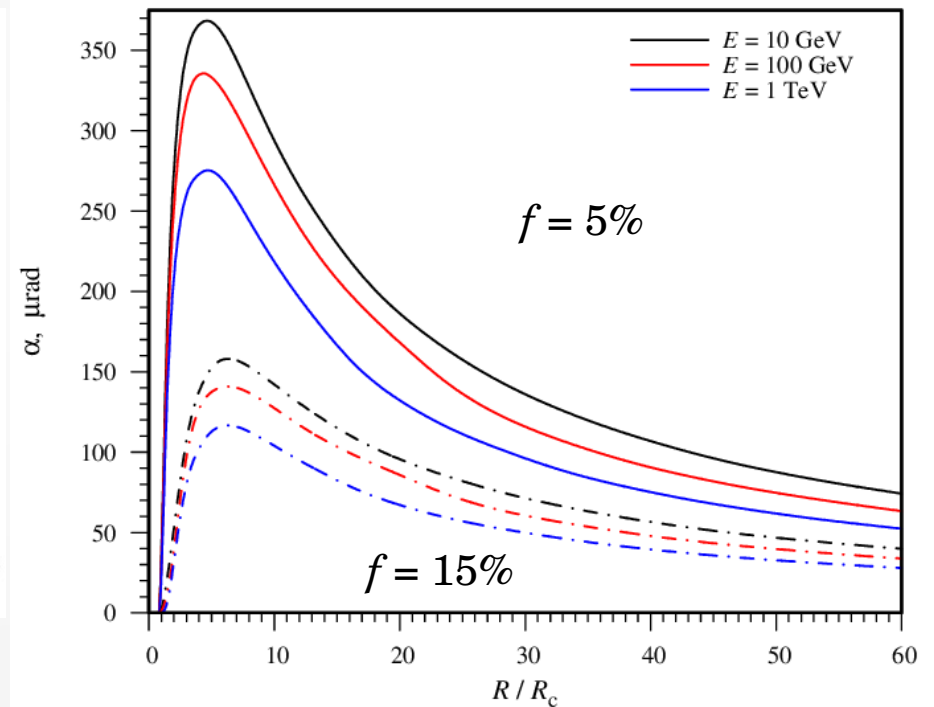
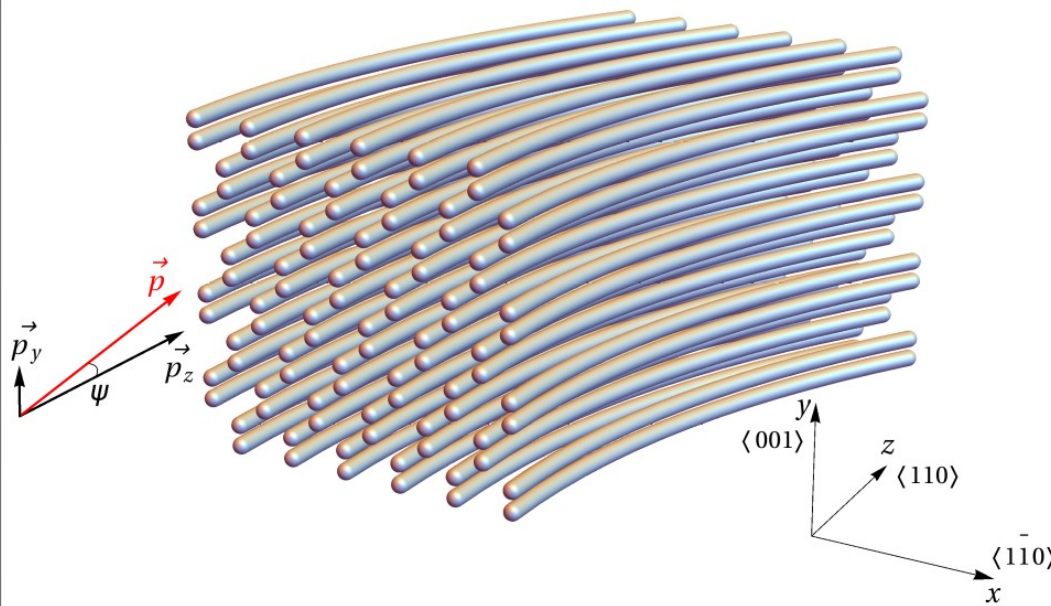
$$\alpha = \frac{L}{R} = \frac{\theta_c^2}{2\xi^2 R \left( \operatorname{erf}^{-1} \left( \frac{f}{1 - \sqrt{\frac{R_c}{R}}} \right) \right)^2}, \quad \theta_c = \sqrt{\frac{2U_0}{E}} \left( 1 - \frac{R_c}{R} \right)$$

$$R = R_{\text{opt}} \Rightarrow \frac{d\alpha}{dR} = 0$$



# Influence of incoherent scattering on planar channeling of high-energy negative particle beams in bent crystals

$\pi^-$ , Si (110)



# Planar potential

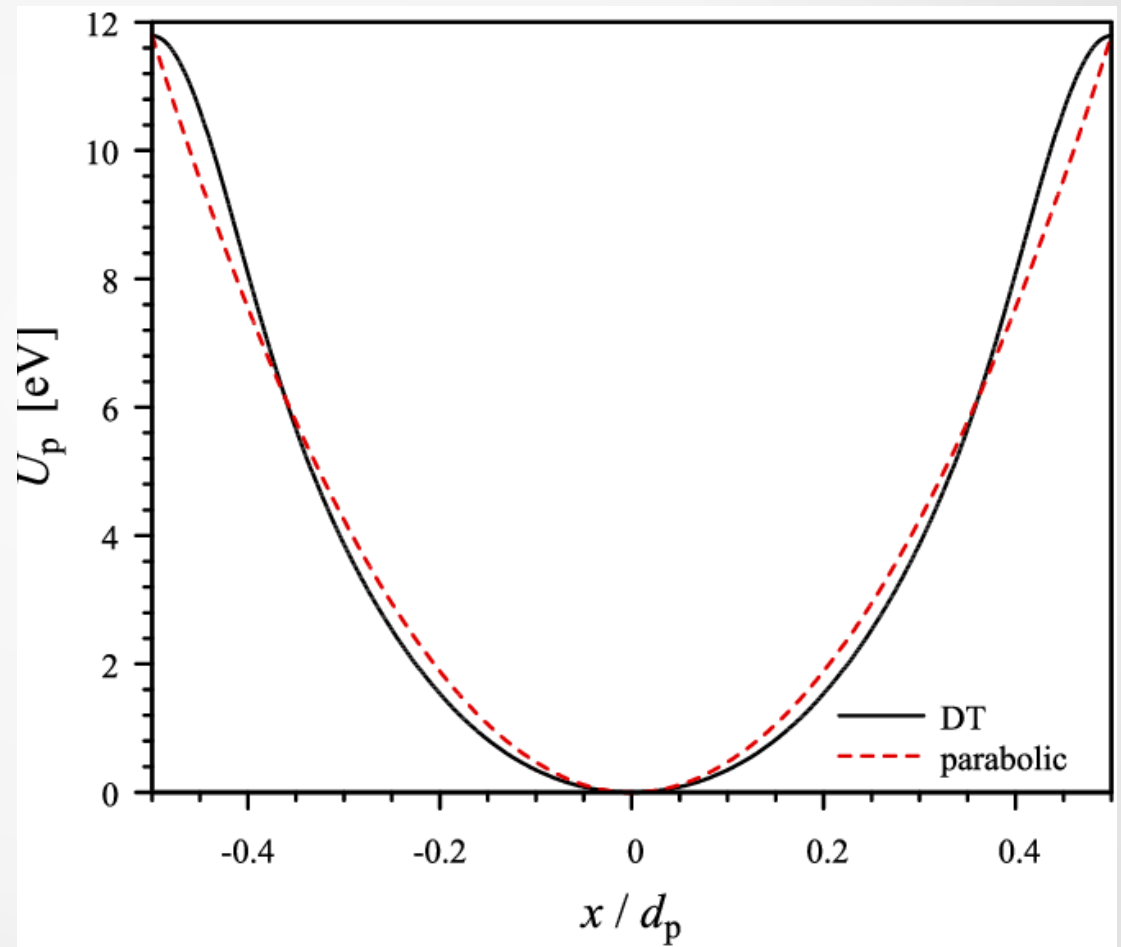
$$\frac{d^2 x}{dt^2} = -\frac{c^2}{E} \frac{d}{dx} U_p(x)$$

$$U_p(x) = U_0 \left( \frac{2x}{d_p} \right)^2$$

$$\frac{d^2 x}{dt^2} = -\frac{8c^2 U_0}{E d_p^2} x = -\frac{4c^2 \theta_c^2}{d_p^2} x$$

$$x = C_1 \cos(\omega_p t) + C_2 \sin(\omega_p t)$$

$$\omega_p = \frac{2c\theta_c}{d_p}$$





# Channeling radiation

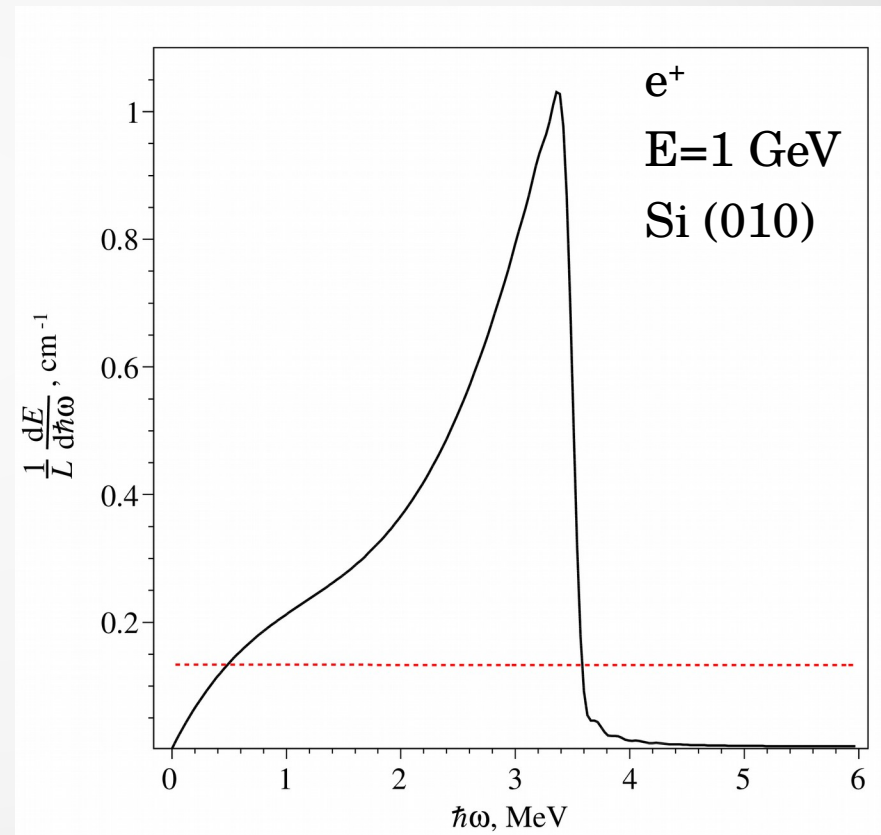
$$\frac{dE}{d\omega} = \frac{e^2 \omega}{2\pi c^4} \int_{\delta}^{\infty} \frac{dq}{q^2} \left( 1 - 2 \frac{\delta}{q} \left( 1 - \frac{\delta}{q} \right) \right) |\vec{W}(q)|^2$$

$$\vec{W}(q) = \int_0^T \dot{\vec{v}} \exp(iqct) dt, \quad \delta = \frac{\omega}{2c\gamma^2}$$

$$U_p(x) = U_0 \left( \frac{2x}{d_p} \right)^2$$

$$\frac{dE}{d\omega} = A_1 \omega_p^2 \omega L \left( 1 - 2 \frac{\omega}{\omega_m} \left( 1 - \frac{\omega}{\omega_m} \right) \right) \Theta(\omega_m - \omega)$$

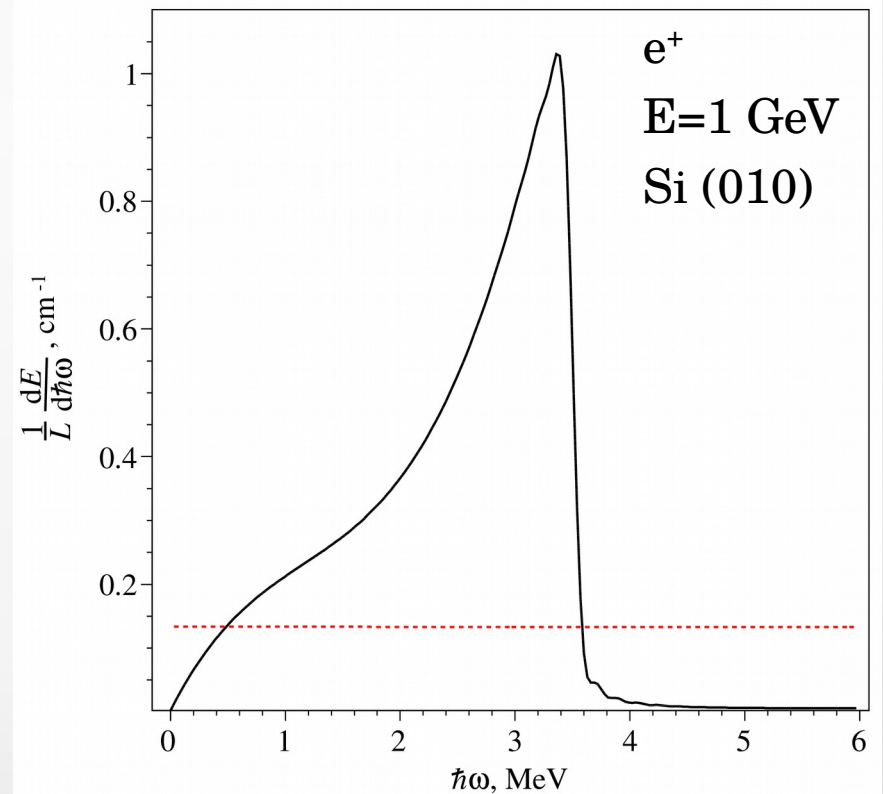
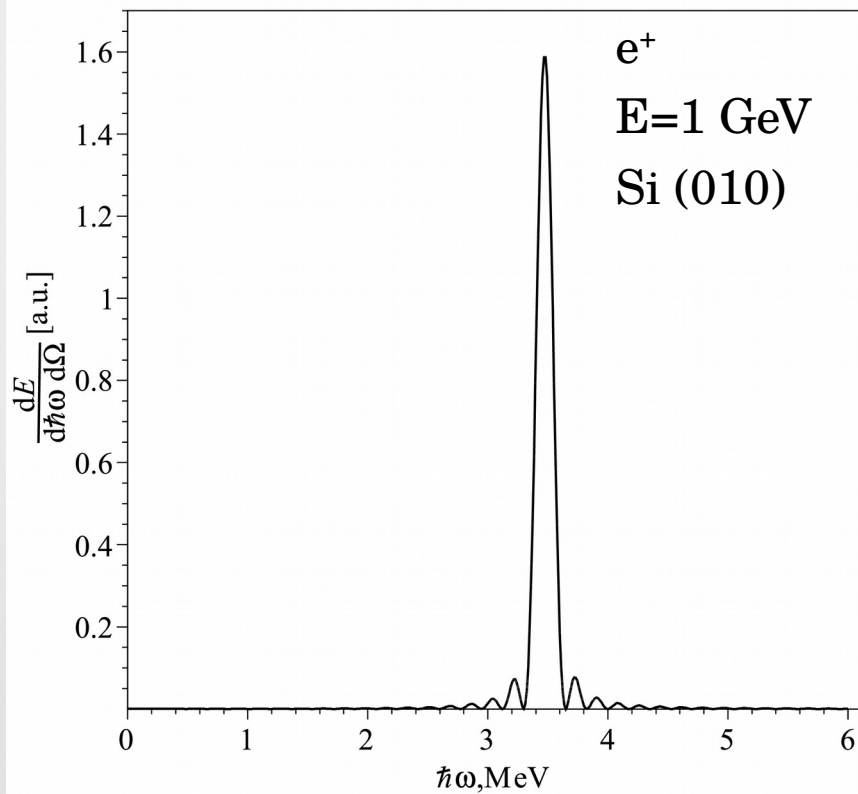
$$\omega_m = \frac{4\gamma^2 c \theta_c}{d_p}$$



$$\hbar \omega_m \approx 3.42 \text{ MeV}$$

# Channeling radiation

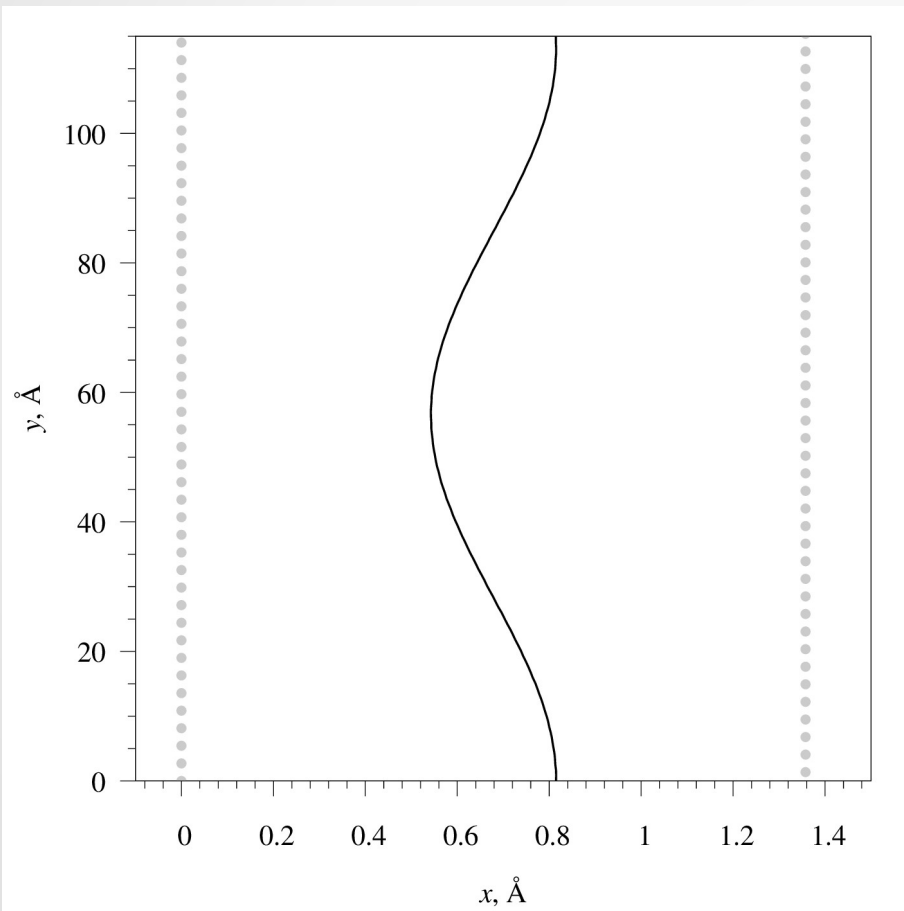
$$\frac{dE}{d\omega d\Omega} = \frac{e^2 \omega}{4\pi^2 c} \left| \int_{-\infty}^{\infty} dt \frac{\vec{n} \times ((\vec{n} - \vec{\beta}) \times \dot{\vec{\beta}})}{(1 - \vec{n} \cdot \vec{\beta})^2} \exp\left(i\omega\left(t - \frac{\vec{n} \cdot \vec{r}}{c}\right)\right) \right|^2$$



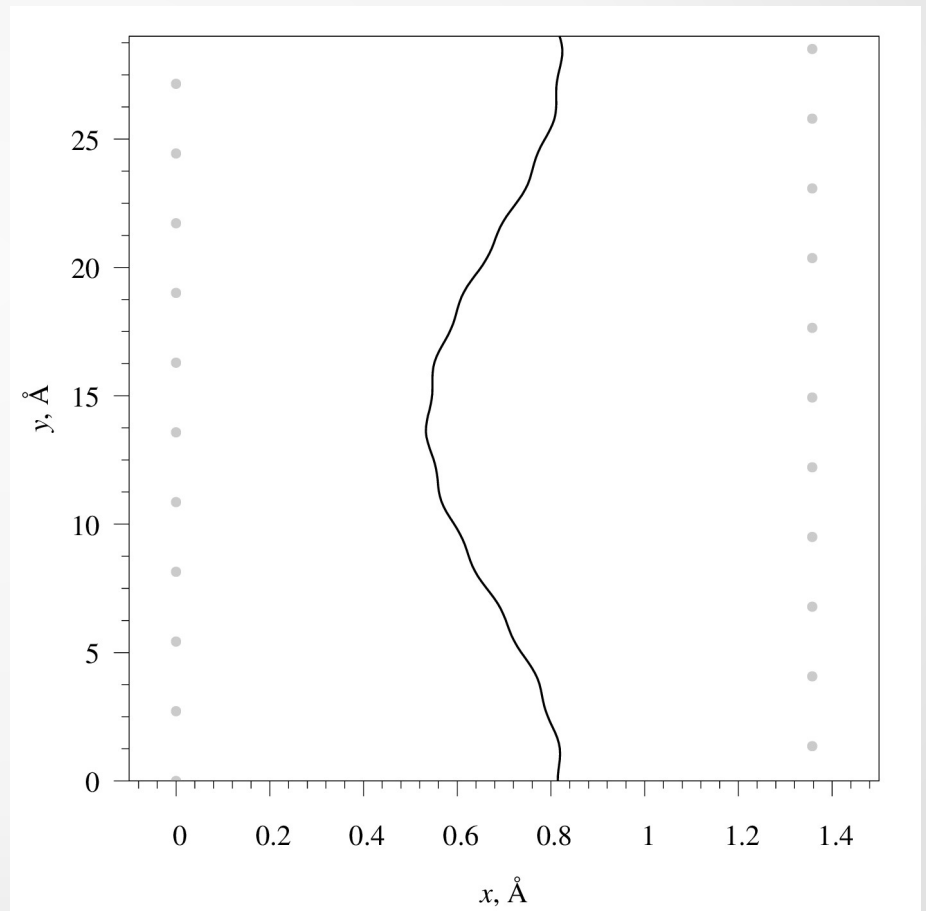
# The effect of scattering on individual atomic strings

$e^+$ ,  $E=1$  GeV, Si (010)

$$\theta_{y,\text{in}} = 10 \psi_c$$



$$\theta_{y,\text{in}} = 2.5 \psi_c$$

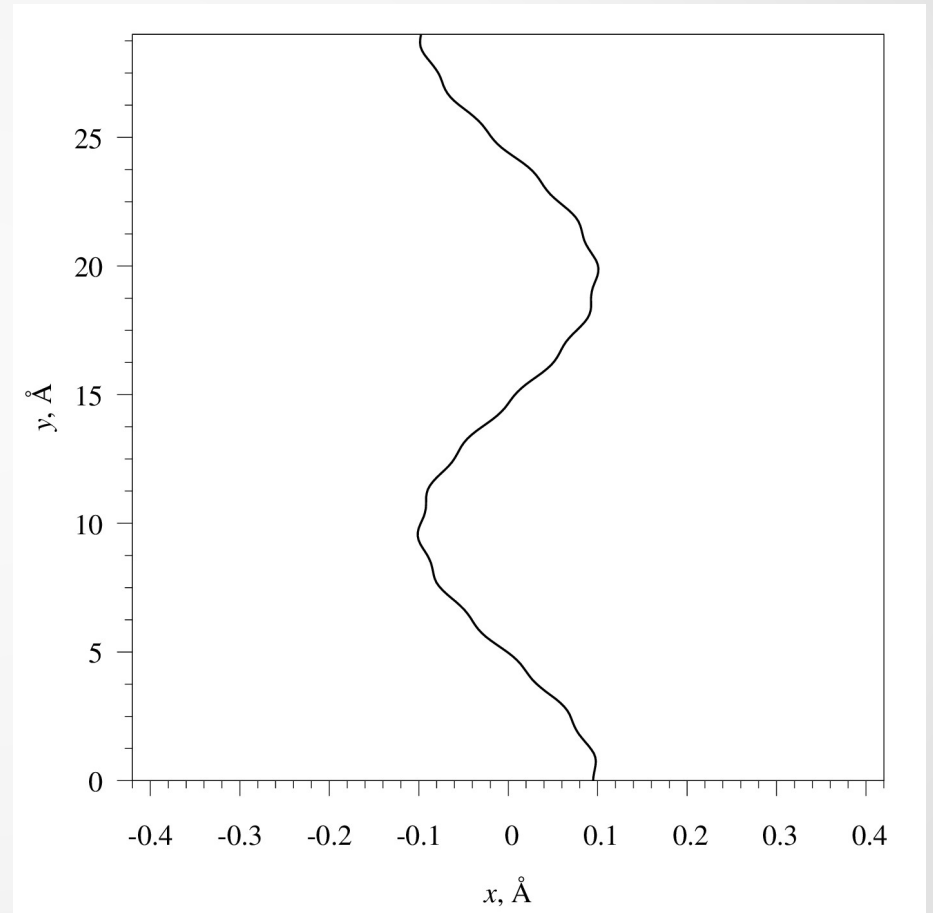


# The effect of scattering on individual atomic strings

$$\frac{d^2 x}{dt^2} = -\frac{4c^2 \theta_c^2}{d_p^2} x + A \cos\left(2\pi \frac{v_y t}{d_s}\right), \quad v_y \approx \theta_y c$$

$$x = C_1 \cos(\omega_p t) + C_2 \sin(\omega_p t) + \frac{A \cos(\omega_s t)}{\omega_p^2 - \omega_s^2},$$

$$\omega_s = \frac{2\pi c \theta_y}{d_s}$$



# The effect of scattering on individual atomic strings

$$\frac{d^2 x}{dt^2} = -\omega_p^2 x + A \cos(\omega_s t)$$

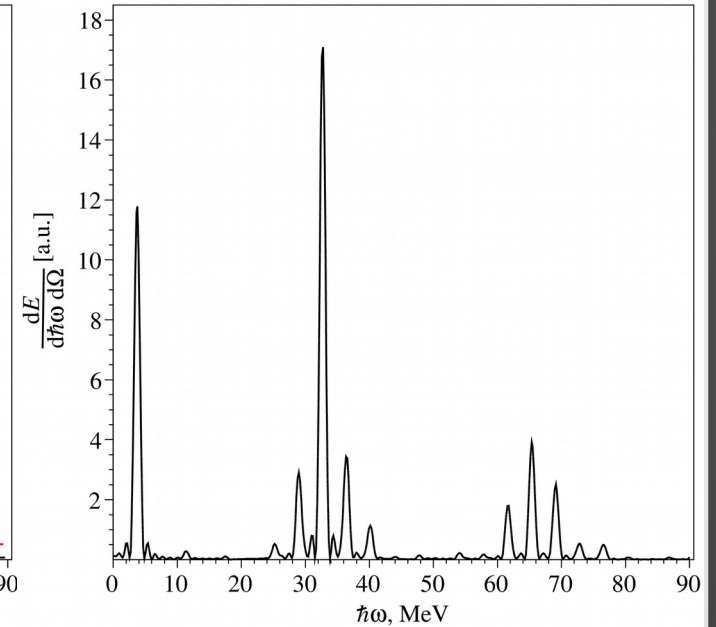
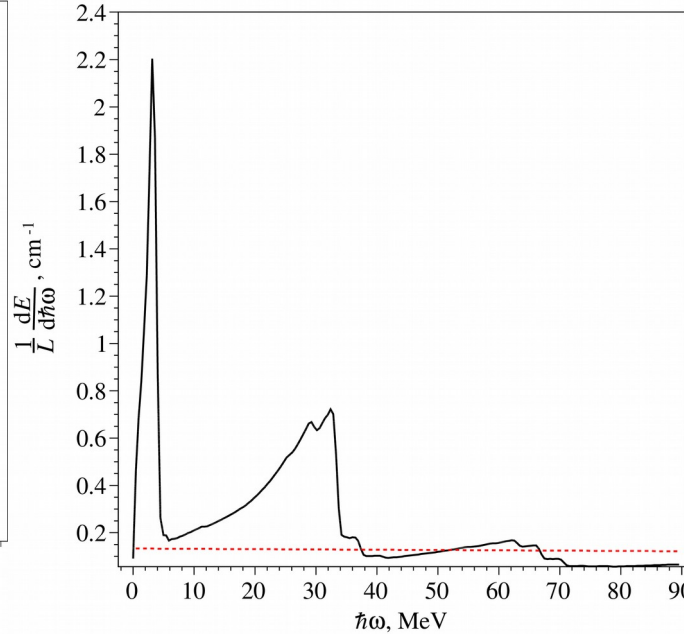
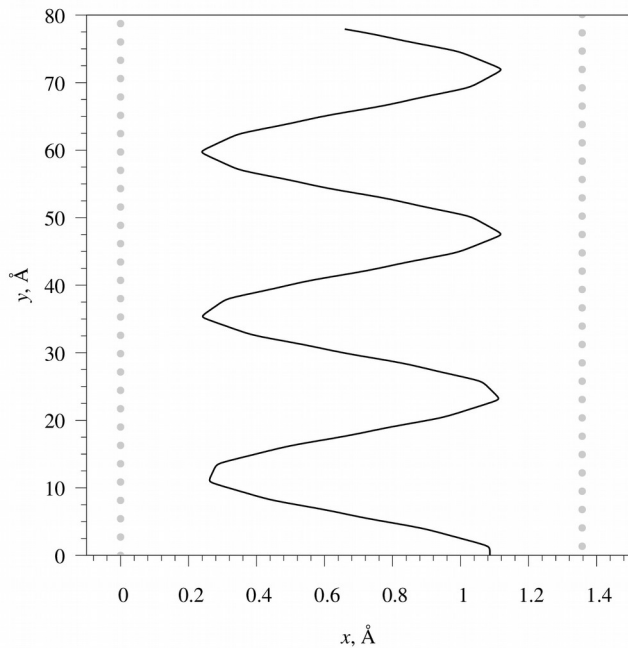
$$\begin{aligned} \frac{dE}{d\omega} = & A_1 \omega_p^2 \omega L \left( 1 - 2 \frac{\omega}{\omega_{mp}} \left( 1 - \frac{\omega}{\omega_{mp}} \right) \right) \Theta(\omega_{mp} - \omega) + \\ & + A_2 \frac{A^2}{(\omega_p^2 - \omega_s^2)^2} \omega_s^2 \omega L \left( 1 - 2 \frac{\omega}{\omega_{ms}} \left( 1 - \frac{\omega}{\omega_{ms}} \right) \right) \Theta(\omega_{ms} - \omega), \quad \text{if } \omega_s \neq \omega_p \end{aligned}$$

$$\omega_{mp} = 2 \gamma^2 \omega_p, \quad \omega_{ms} = 2 \gamma^2 \omega_s, \quad \omega_{ms} \propto \theta_y$$

# The effect of scattering on individual atomic strings

$e^+$ ,  $E=1$  GeV, Si (010),  $L = 8.16 \mu\text{m}$

$$\theta_{y,\text{in}} = 2.5 \psi_c \approx 0.96 \text{ mrad}$$



$$\omega_{\text{mp}} = 2 \gamma^2 \omega_p \approx 3.4 \text{ MeV}, \quad \omega_{\text{ms}} = 2 \gamma^2 \omega_s \approx 33.7 \text{ MeV}$$

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*Thank you for excellent school you make  
every year!*

*For lecturers:*

*Thank you for your interesting speeches  
and your work with students!*

*For students:*

*Thank you for your attention!*